

Development of the Timepix4 chip



on behalf of the Medipix4 collaboration (<https://medipix.web.cern.ch/>)

Vladimir Gromov

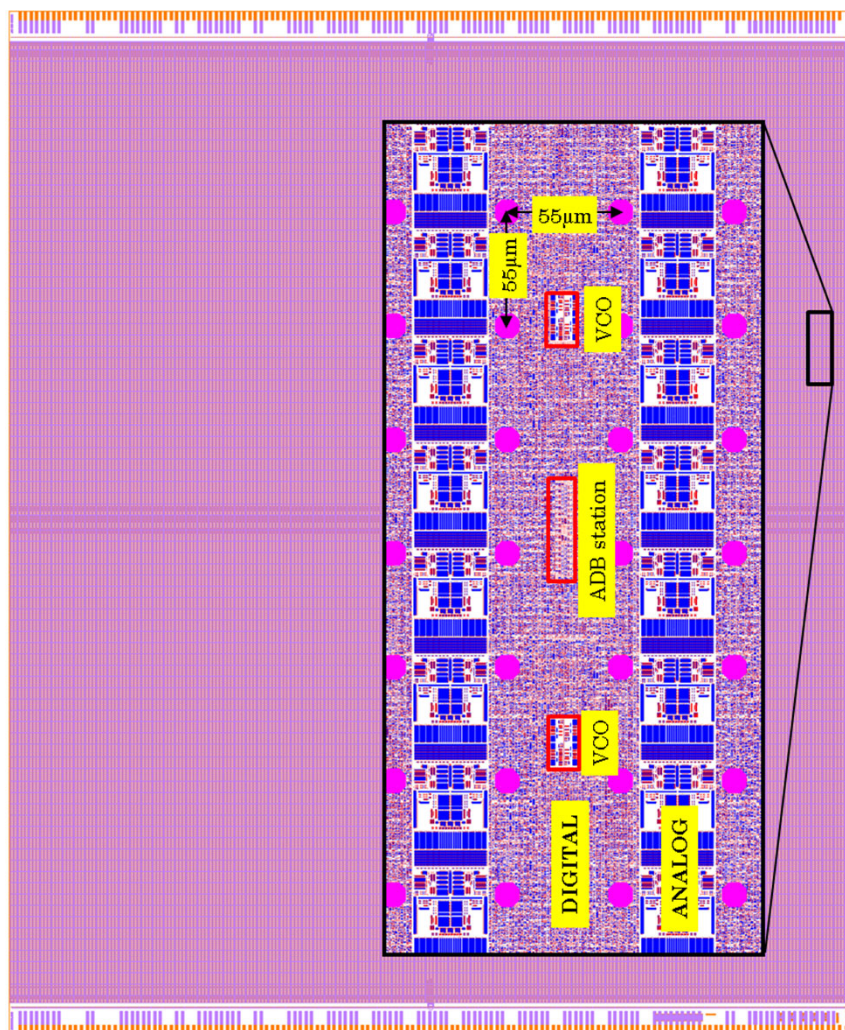
National Institute for Subatomic Physics (Nikhef), Amsterdam, the Netherlands

- introduction and main features of the Timepix4 chip
- the circuit design aspects
- applications opportunities
- experimental results
- summary

introduction

Timepix4: Readout ASIC for hybrid pixel detectors

Single hit (electrical signal) pixel-level processor



Features of the Timepix4 chip

technology			TSMC 65nm - 10 metal
pixel size			55 x 55 μm
chip arrangement			4-side buttable 3x “hidden” periphery TSV I/O pixel matrix: 512 x 448
sensitive area			6.94 cm²
interface			3x 147 I/O TSV / Wirebond
Readout Modes	Tracking (data driven)	mode	ToT & ToA
		data	64-bit per hit
		max hit rate	3.58x10 ⁶ hits/mm ² /s (10.8 KHz / pixel)
	Imaging (frame-based)	Mode	CRW: Pixel Counter (8 /16-bit)
		frame rate	up to 89kFPS
		max hit rate	~ 5 x 10 ⁹ hits/mm ² /s
Energy resolution @ Si sensor			~ 1keV FWHM
ENC @ Cin = 75fF			80e ⁻ rms
minimum threshold			~ 500 e ⁻
hit arrival timing (ToA)			LSB=195ps , range: 1.638ms
charge measurement (ToT)			accuracy: 80e ⁻ rms, range:200ke ⁻
data readout bandwidth			≤163.84 Gbps (16x @ 10.24 Gbps)
Power Supply Voltage			1.2V
Power			~3.5W

➤ Timepix4 is a fully digitally-controlled, 4-side tillable large-area, single threshold pixel readout chip with improved energy and time resolution and with high-rate imaging capabilities

Particle identification and tracking

Photon (hit) detection time-resolved & energy-resolved :

- High-Energy Physics (HEP):
 - very high rate pixel telescope
 - ultra-fast sensor studies for HL-LHC)
 - beam gas interaction (PS SPS/LHC)
 - ATLAS background rad monitor and TRD detector
 - large area gas-filled TPC for ILC)
- Time-of-flight mass spectrometry
- Neutron time-of-flight imaging
- Radiation monitors
- Electron microscopy
- X-ray and powder diffraction
- Compton camera for medical diagnostics
- Gamma and neutron imaging for nuclear industry and Homeland Security

Imaging applications:

- X-ray imaging in synchrotrons with extreme high rates $> 10^9$ particles/mm²/s

20th Anniversary Symposium on Medipix and Timepix

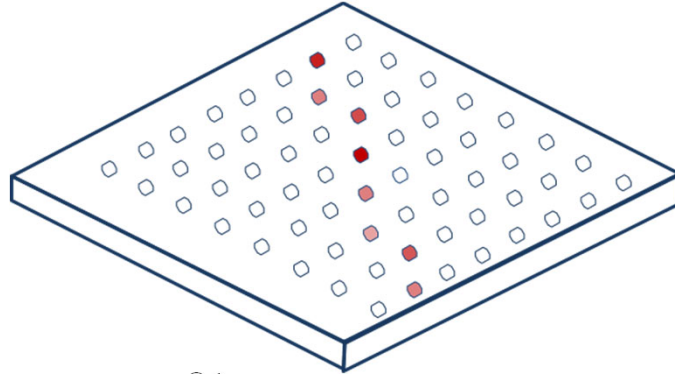
<https://indico.cern.ch/event/782801/>

- **Timepix4 a multi-application device is not fully optimized for a particular application**

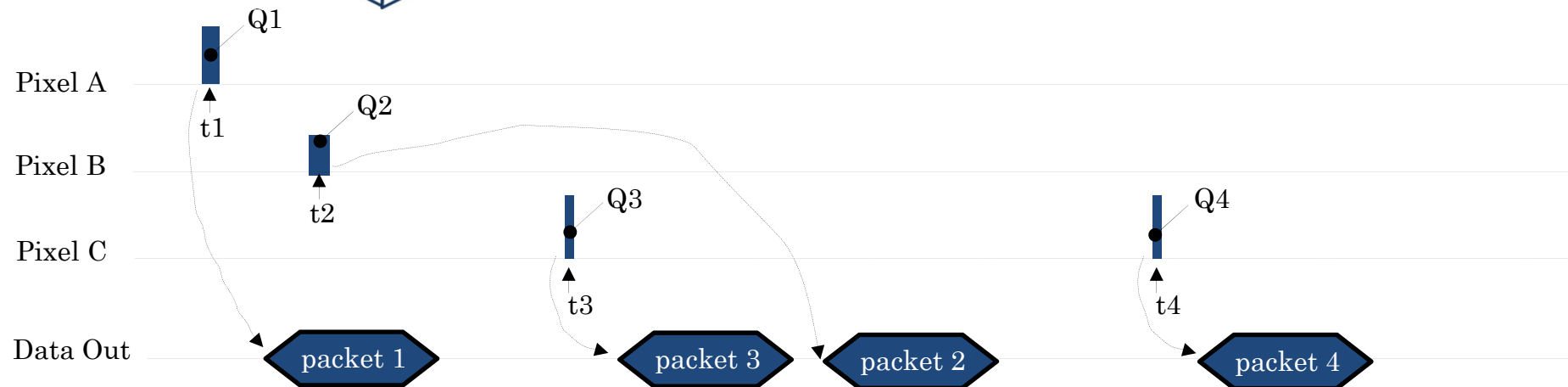
main features

Tracking readout mode: particle track detection / energy-resolved and time-resolved photon (hit) detection

Sparsely distributed hits: zero data-suppressed, continuous, Data-Driven readout



output bandwidth max / min	hit rate	
	per pixel	per mm ²
163 Gbps	10.8 KHz	3.58 MHz
40 Mbps	2.6 Hz	860 Hz



Data Packet <63:0> = pixel address <63:46>, timing data ToA <45:17>, charge(energy) data ToT <16:1>, Pileup <0:0>

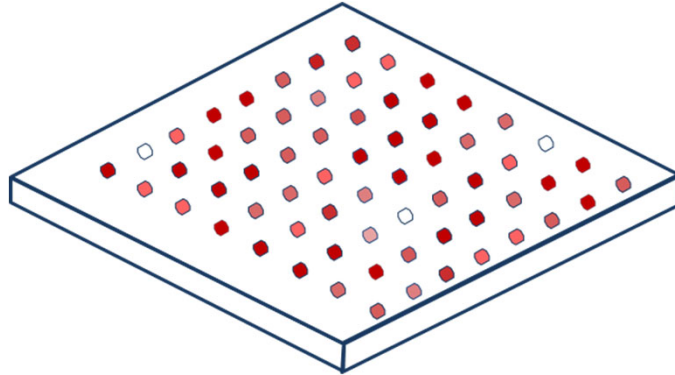
- the data packet is created and read out immediately after the hit occurred
- the bandwidth of the data readout system can be adjusted to match the hit rate
- the hit charge info (ToT) can also be used for the correction of the time info (ToA)

Imaging readout mode : on-pixel hit counting

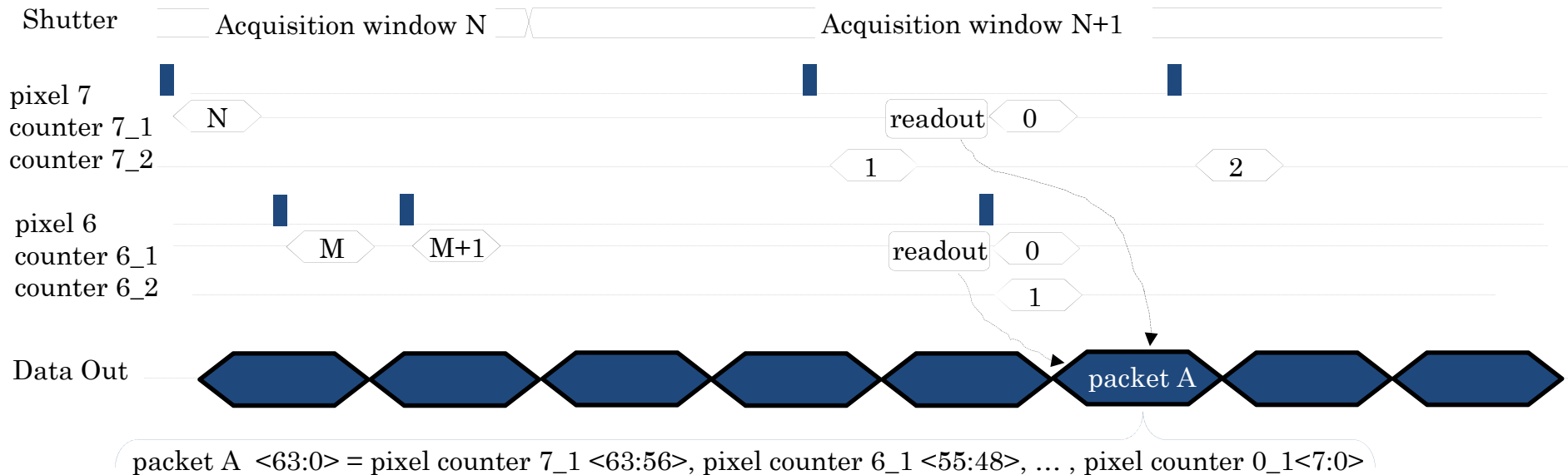
Continuously distributed hits: full frame readout with continuous read-write (CRW)

- NO zero data suppression

- 8-bit or 16-bit pixel counter depth



output bandwidth max / min	Frame rate		hit rate per mm ²
	8-bit counter	16-bit counter	up to 5 GHz
163 Gbps	89 KHz	45 KHz	
40 Mbps	21 Hz	11 Hz	



- continuous data taking and pixel matrix readout with two hit counters per pixel
- the on-pixel hit counter is read out regularly once per frame

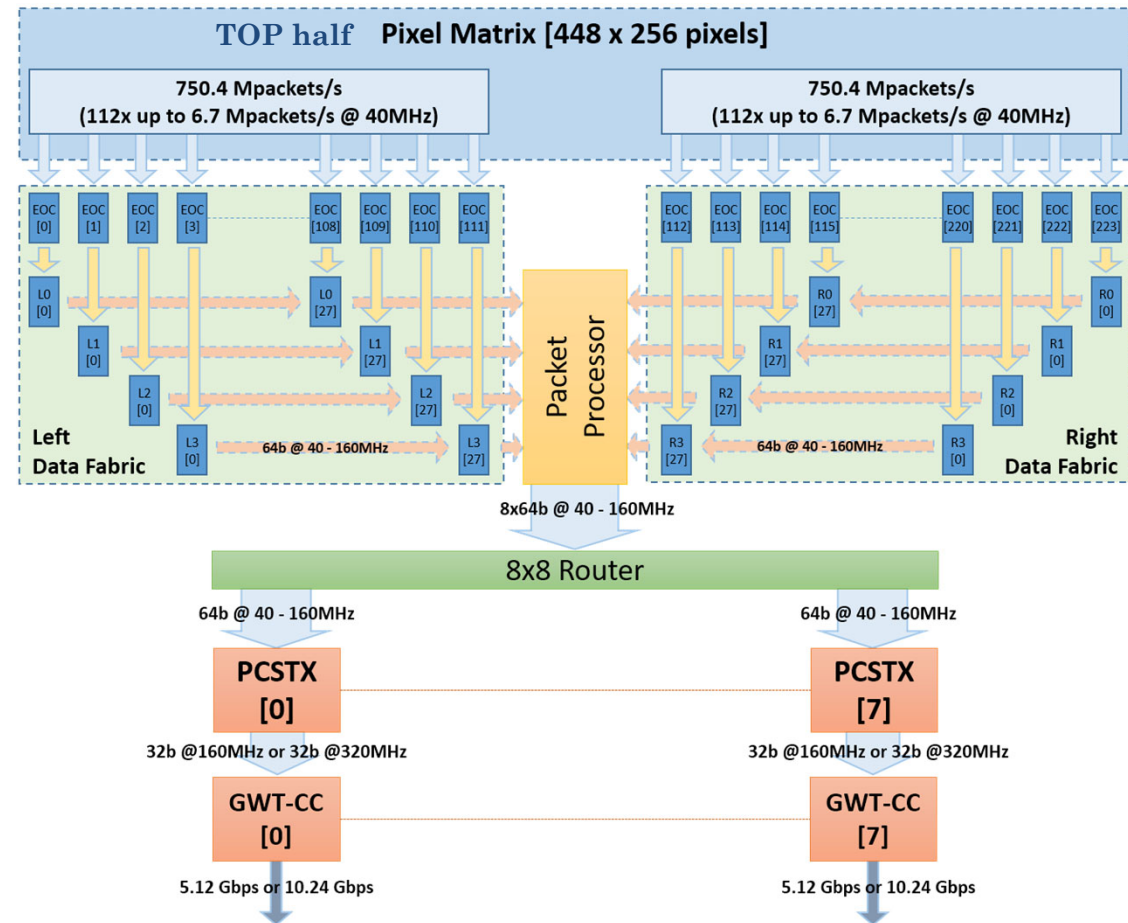
High-volume and high-speed data readout

Data transport architecture

Pixel Matrix → End-of-Column
max bandwidth : 95.6 Gbps

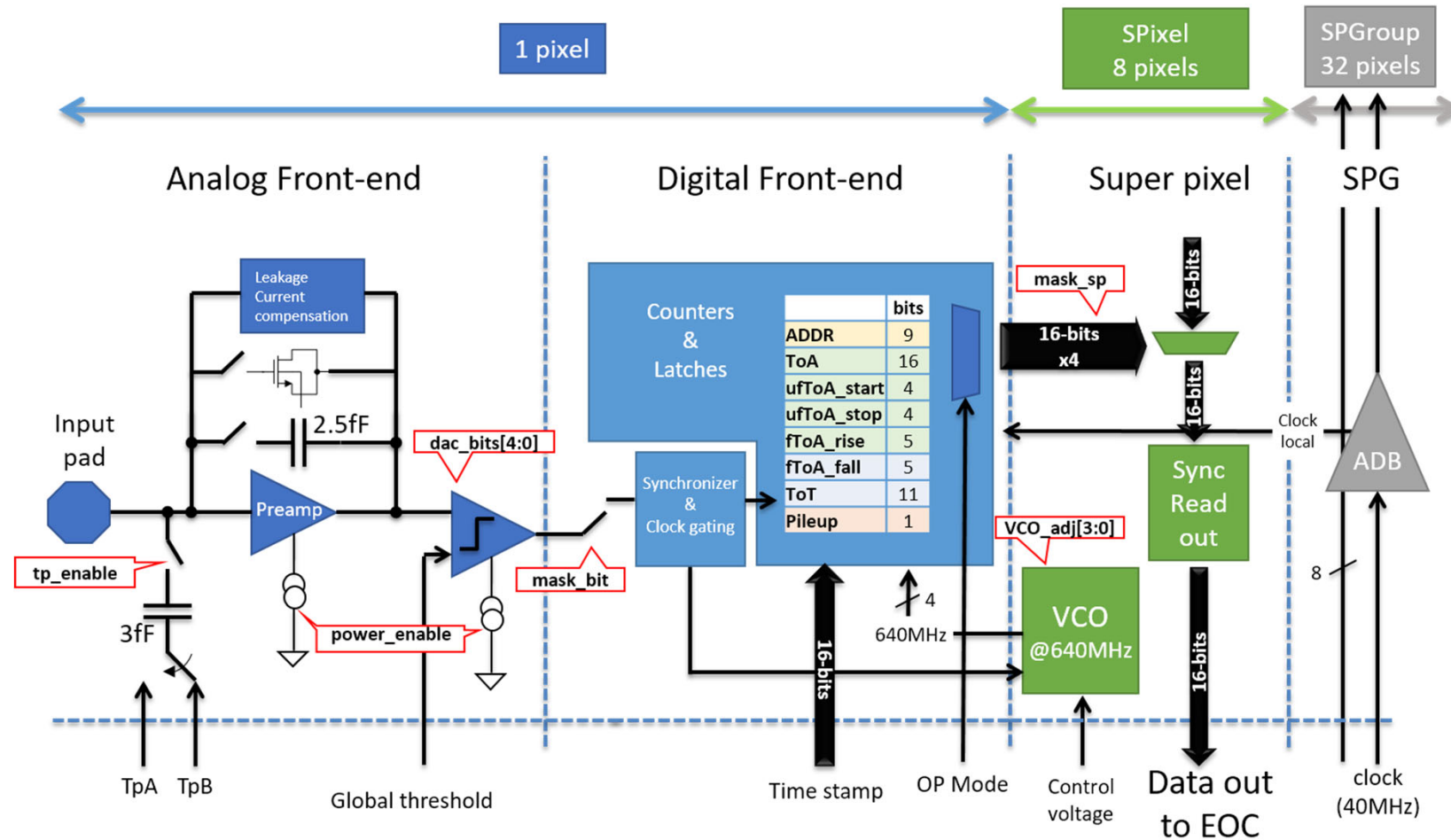
End-of-Column → End-of-Chip
max bandwidth : 81.92 Gbps

output Serializers
max bandwidth : 81.92Gbps



- the bandwidth of the data readout is high up to 163.8 Gbps : 2.56×10^9 packets / sec
: 89×10^3 frames / sec
- the bandwidth the data transport components match to each other
- multi-level FIFO architecture with the push-back overflow control

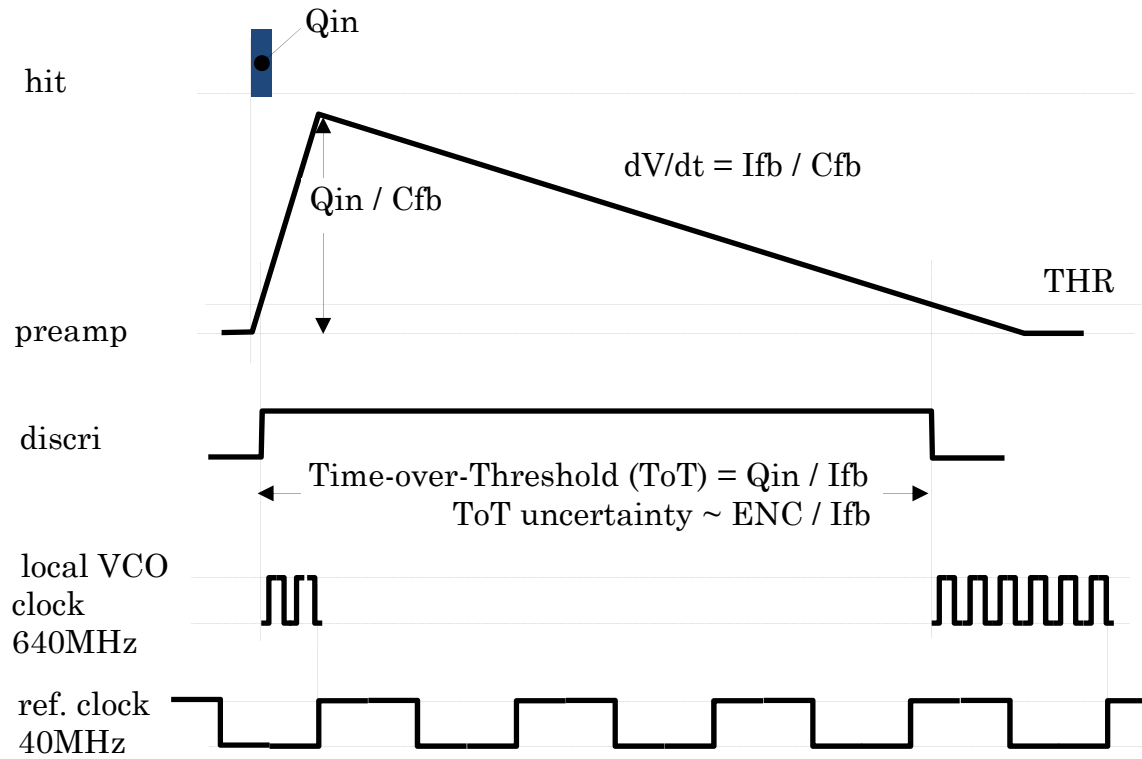
In-pixel signal processing



- the pixel-level circuit :
 - digitizes all the information contained in the hits
 - adds pixel coordinate information
 - sends the data packet to the periphery of the chip
- the local oscillator (VCO) starts to generate a 640MHz clock when it is triggered by the hit. The VCO runtime is limited by the period of a 40MHz reference clock to 25ns

Hit charge quantization : Time-over-Threshold method (ToT)

Charge sensitive amplifier (CSA) with a Krummenacher feedback network ($I_{fb} = I_{KRUM} = \text{const}$)



ToT quantization error: $T^{640\text{MHz}} = 1.6\text{ns} / \sqrt{12} = 0.5\text{ns rms}$

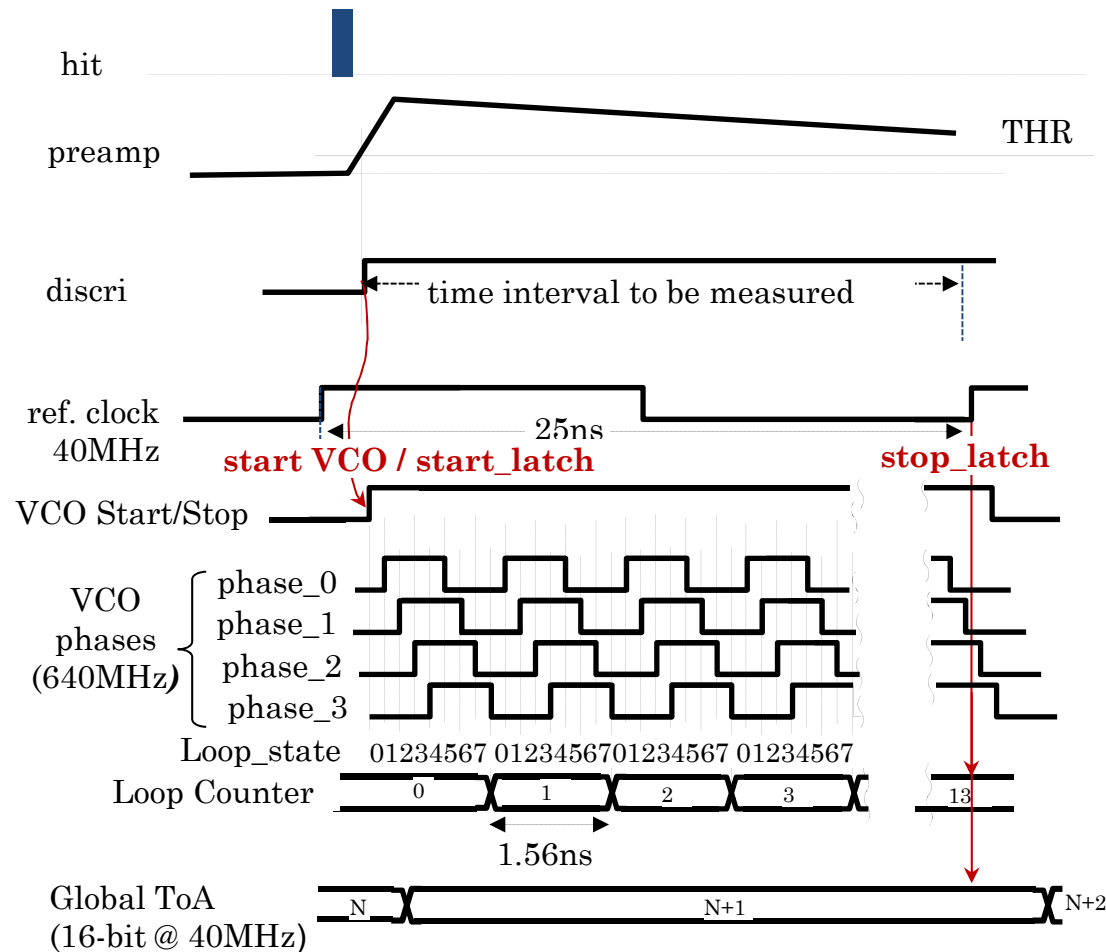
ToT quantization range: 11 bit counter @ 40MHz clock = 51us

		e ⁻ collection	h ⁺ collection	h ⁺ collection (log gain)
Gain=1/Cfb		40mV/ke ⁻	40mV/ke ⁻	25mV/ke ⁻
ENC Cin=75fF		80e ⁻ rms	80e ⁻ rms	90e ⁻ rms
THR (min)		500e ⁻	500e ⁻	600e ⁻
ToT range		250ke ⁻	200ke ⁻	800ke ⁻
I _{KRUM} = 18nA	ToT uncertainty	0.6ns rms 0.7ns rms		
	ToT quantization error	0.5ns rms ~63e ⁻ rms		
I _{KRUM} = 1nA	ToT uncertainty	13ns rms	13ns rms	15ns rms
	ToT quantization error	0.5ns rms ~ 3e ⁻ rms		

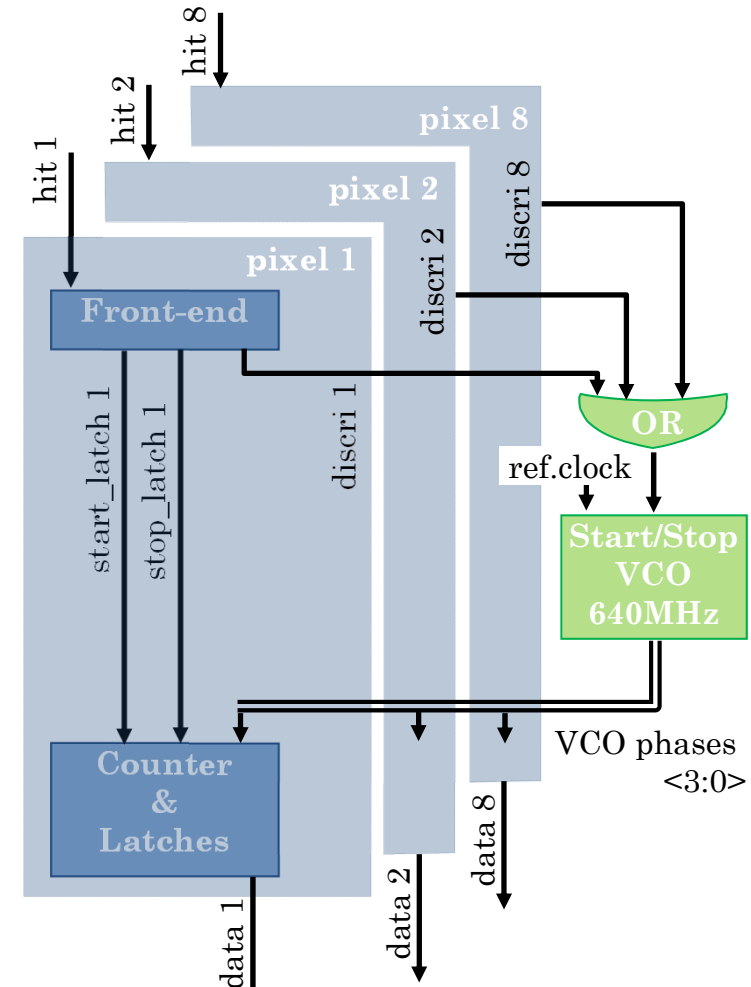
- a 640MHz local VCO clock pulses and a 40MHz reference clock pulses pass through the clock gating block and are counted giving the digital representation of the measured charge Q_{in}
- the range of the ToT method is limited by the value of the charge-storing capacitance $C_{in} + C_{fb}$
- the precision of the ToT method is limited by the noise ($ENC = 80e^- \text{ rms}$)
- this corresponds to a 288eV rms energy resolution in silicon sensors ($3.67\text{eV}/e^-$)

Hit arrival time (ToA) quantization : a 195ps TDC per pixel

Time-to-digital conversion : the signals



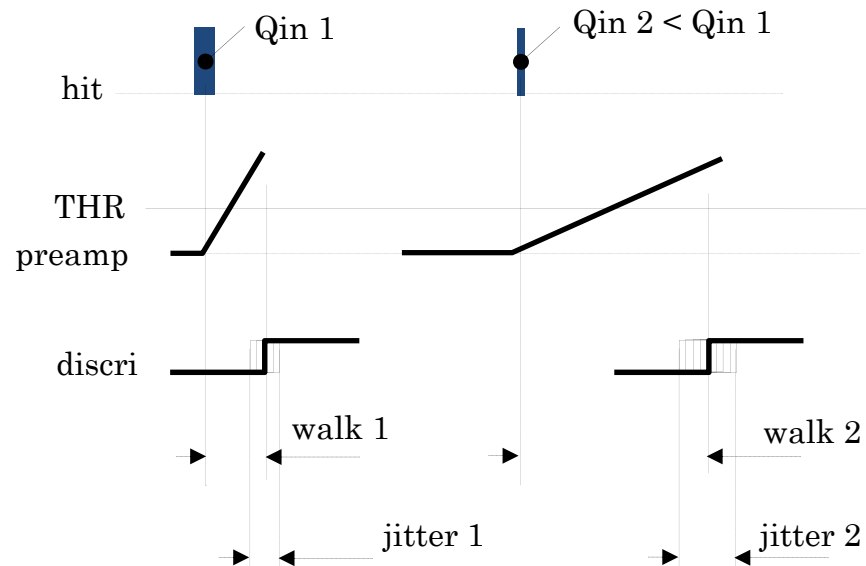
TDC block diagram



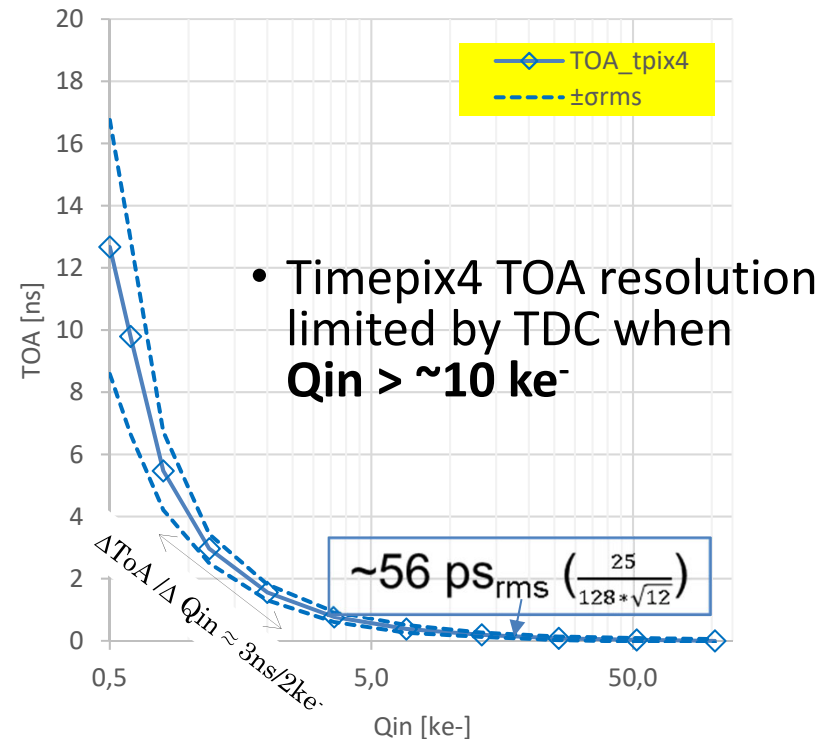
- the resolution of the TDC is limited by the size of the VCO loop state ($195\text{ps} = 1/640\text{MHz} / 8$)
- the dynamic range of the TDC is set by duration of the global timing orbit ($1.638\text{ms} = 16\text{bit}@40\text{MHz}$)
- the VCO consumes significant current ($\sim 500\mu\text{A}$) when it is running
- the VCO power consumption is negligible due to a low running duty cycle ($\sim 10^{-3}$)

Hit arrival time (ToA) : accuracy limiting effects

Time-walk & noise time-jitter



ToA (Q_{in}) @ THR=500e⁻, ENC=60e⁻rms (simulated by R. Ballabriga)

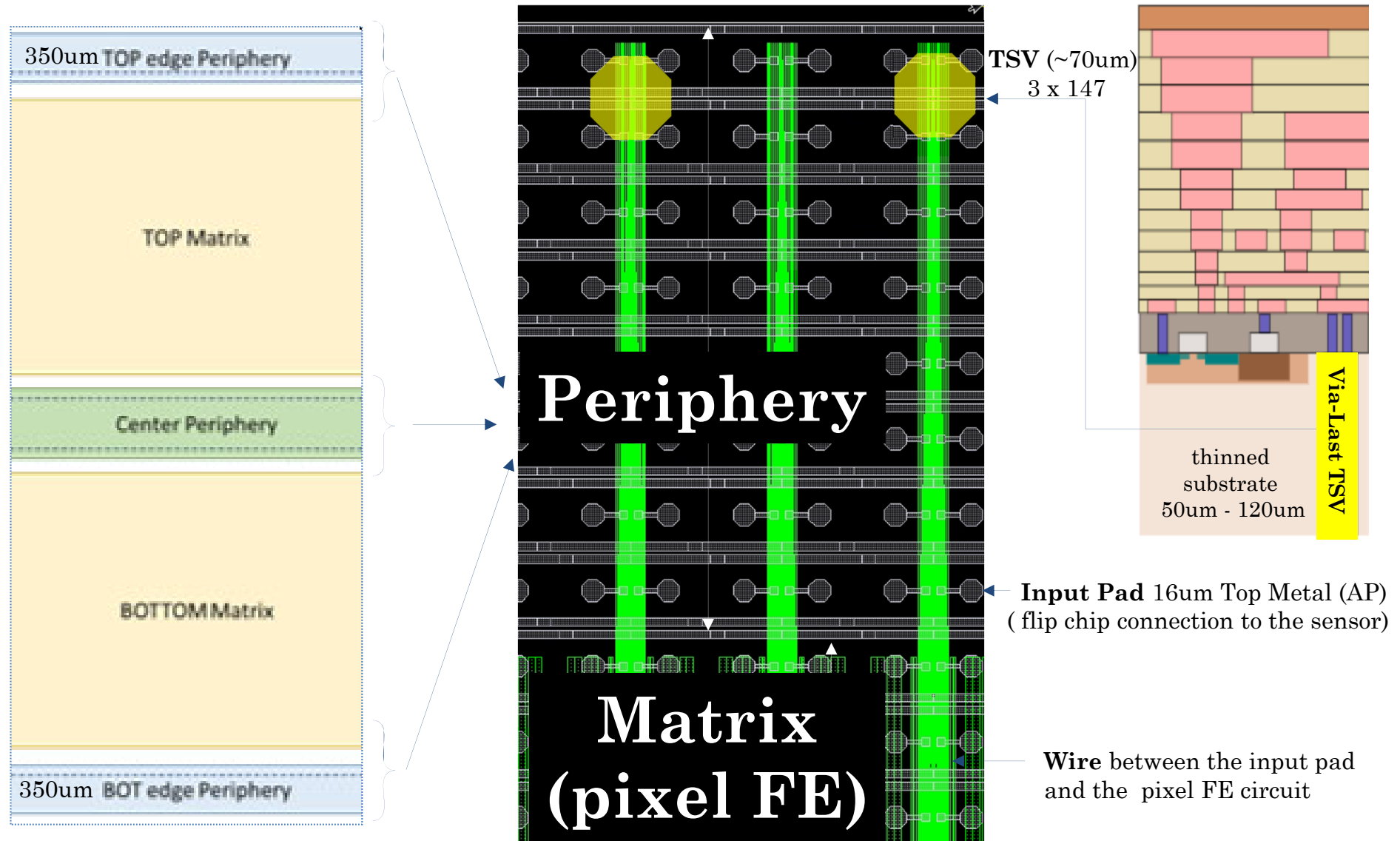


- the performance of the Front-end circuit (preamplifier, discriminator) limits the accuracy of the timing measurements (time-walk, noise time-jitter)
- a 195ps ToA accuracy can be achieved only for the large-size hits with $Q_{in} > 10 \text{ ke}^-$
- the ToT charge information will be used to identify the large-size hits
- for small-size hits ($< 10 \text{ ke}^-$) : - the ToA @ ToT time-walk correction is feasible

$$\text{ToA rms} = \text{ToT rms} \cdot \Delta\text{ToA}/\Delta Q_{in} = 80 \text{e}^- \text{ rms} \cdot 3000 \text{ps}/2000 \text{e}^- = 120 \text{ps rms}$$

- however the ToA noise jitter is still very high $\gg$ LSB (195ps)

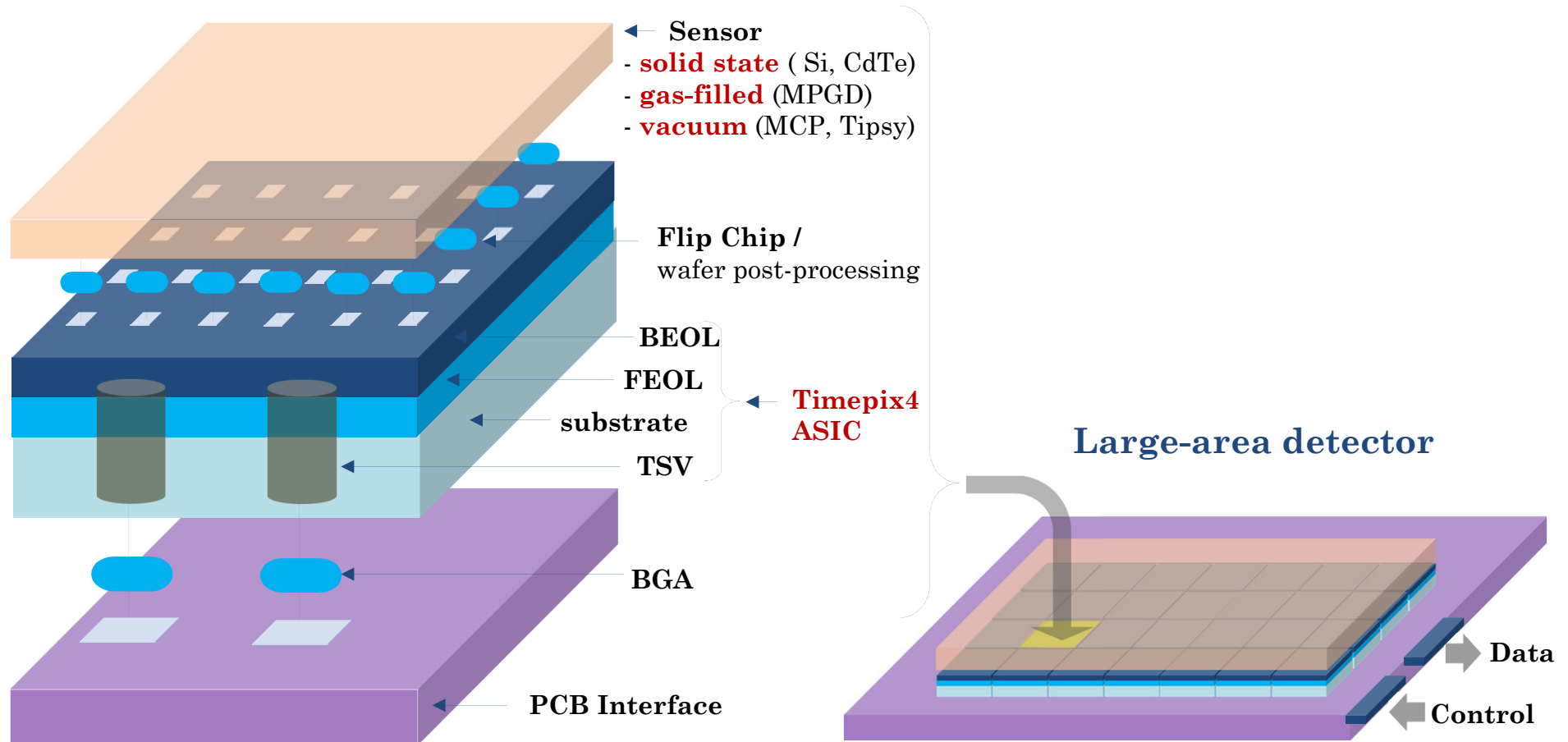
“Hidden” peripheries with TSV (Through-Silicon-Vias)



➤ chip surface utilization is high > 99.5% active area

4-sides stitching of the Timepix4 ASIC-level modules

Timepix4 ASIC-level Hybrid detector module



- the TSV technology allows for a 4-sides stitching of the ASIC-level modules to construct large-area detectors
- the large-area detector is almost-dead-area-free : > 99.5% active area

the circuit design
aspects

Design Strategy & Top Level Integration (X. Llopart)

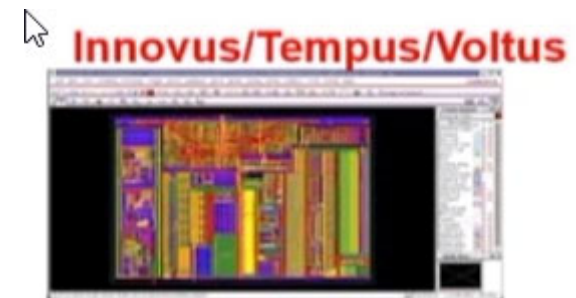
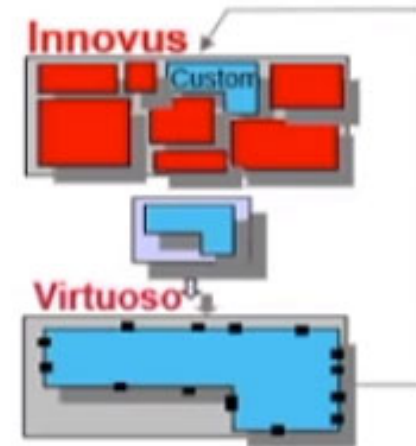
- Design specifications closed 2 years ago
- Top level chip floorplan realized at a very early stage
- Use the digital on top flow
 - All analog blocks designed as “islands” inside digital flow
 - Required careful physical and functional characterization before integration
 - Digital logic is used as “glue” between analog blocks
- Use of UVM as system level functional verification
 - Allows full chip top level simulations → Impossible using analog simulators
- Extensive use of repositories (GitLab, ClioSoft) allowed versioning and save file sharing between the design team
- Total design time of ~3 years with 9 engineers → ~12.5 FTE
- ASIC designers:

CERN (Geneve): R. Ballabriga, T. Poikela,

E. Santin, V. Sriskaran, N. Egidos, X. Llopart

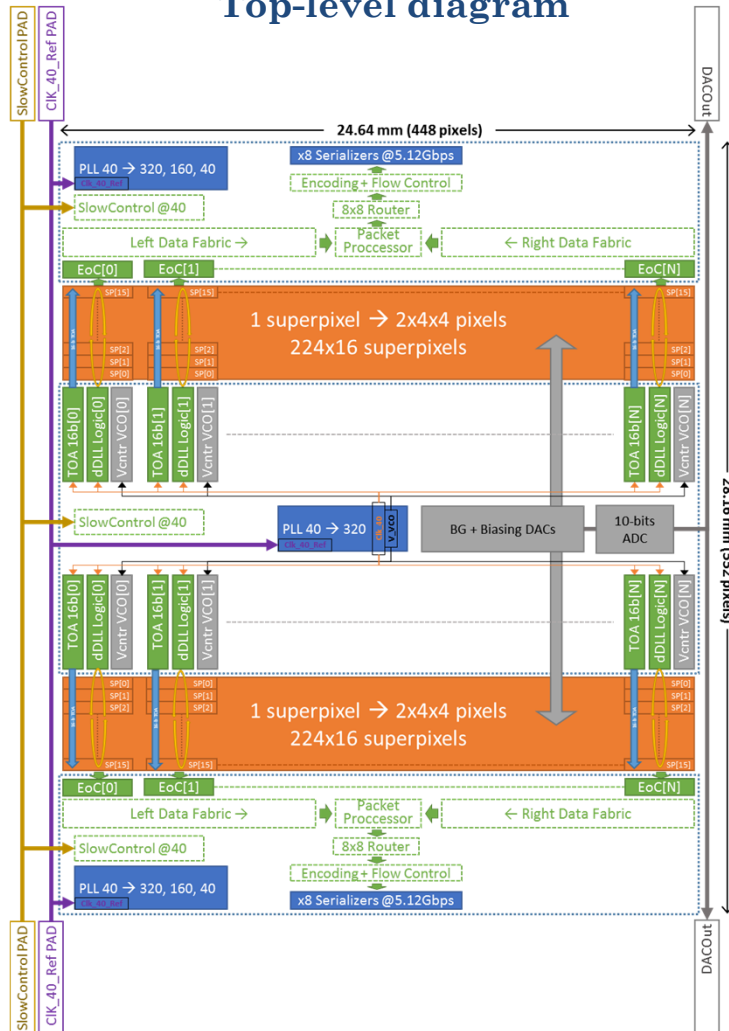
Nikhef (Amsterdam): V. Gromov , A. Vitkovskiy

IFAE (Barcelona): R. Casanova



Timepix4: Floorplan and Interface

Top-level diagram



High-Speed data Readout :

- 16 x 5.12 Gbps / 10.24 Gbps Serial links ($\pm 0.6V$ @ $R_{term}=100 \Omega$)

Custom Slow Control protocol:

- write / read configuration registers
- pixel matrix configuration > 2 Mb (8-bit/pixel + 24-bit/SPGroup)
- peripheral registers (DAC settings, operation modes, e-fuses,)
- readout pixel matrix in the test mode @ 40MHz
- point-to-point connection between the chip and the readout system

I2C control protocol:

- on-chip adapter from I2C slave to the Slow Control

Global control signals:

Data Acquisition time window (SHUTTER)
Synchronization of Global Time Stamp counter (TO_SYN)
External reset (RESET)

Resets procedure:

- periphery logic reset : concurrent
- pixel matrix reset : sequential

External clocks:

- Slow control clock (< 40MHz) (SC_CLOCK_IN)
- PLL Clock reference (40MHz / 320MHz) (CLK_REF_PLL)
- I2C Clock (SCL_I2C)

Internal clock generation:

- configurable PLL circuits (320MHz / 640MHz outputs)

Monitoring / debugging :

- internal-generated analog signals via an on-chip ADC (DAC_OUT)
- internal digital signals (TEST_OUT)

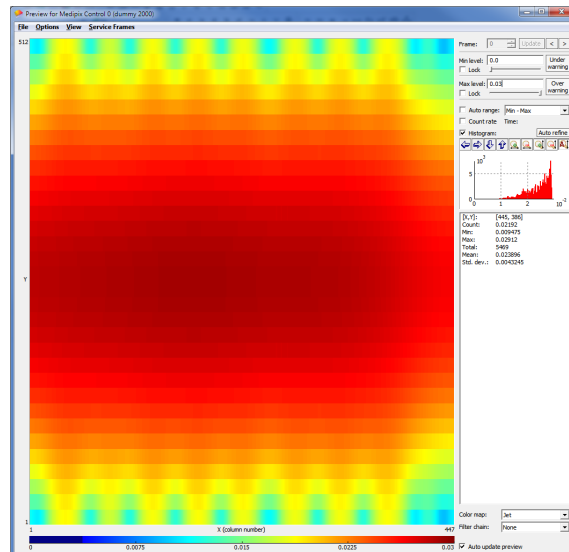
➤ the chip can be controlled/readout in either single-periphery or multi-periphery configuration

Uniformity of the power supply voltage across the chip

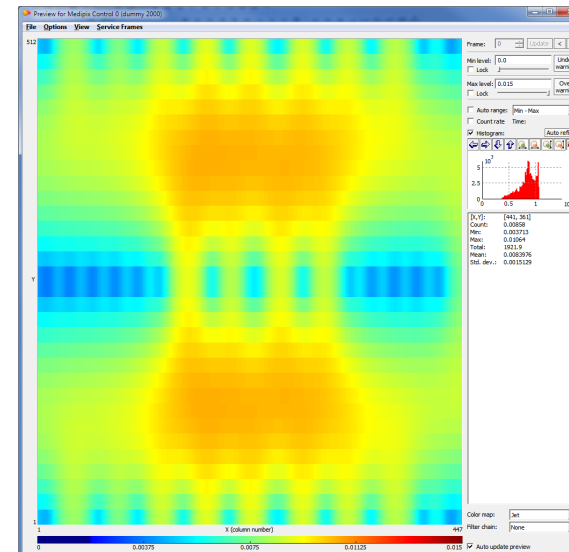
Analog (static) power supply distribution (simulated by X. Llopart)

		2WB	3TSV
Nominal Analog Power [10 μ A/pixel]	V_{drop} [max-min]	19.6 mV	6.9 mV
	I _{max} pad	60 mA	57 mA
Low Analog Power [1 μ A/pixel]	V_{drop} [max-min]	1.96mV	0.69mV
	I _{max} pad	6 mA	5.7 mA

double-side
Wire-Bond (WB) I/O pads



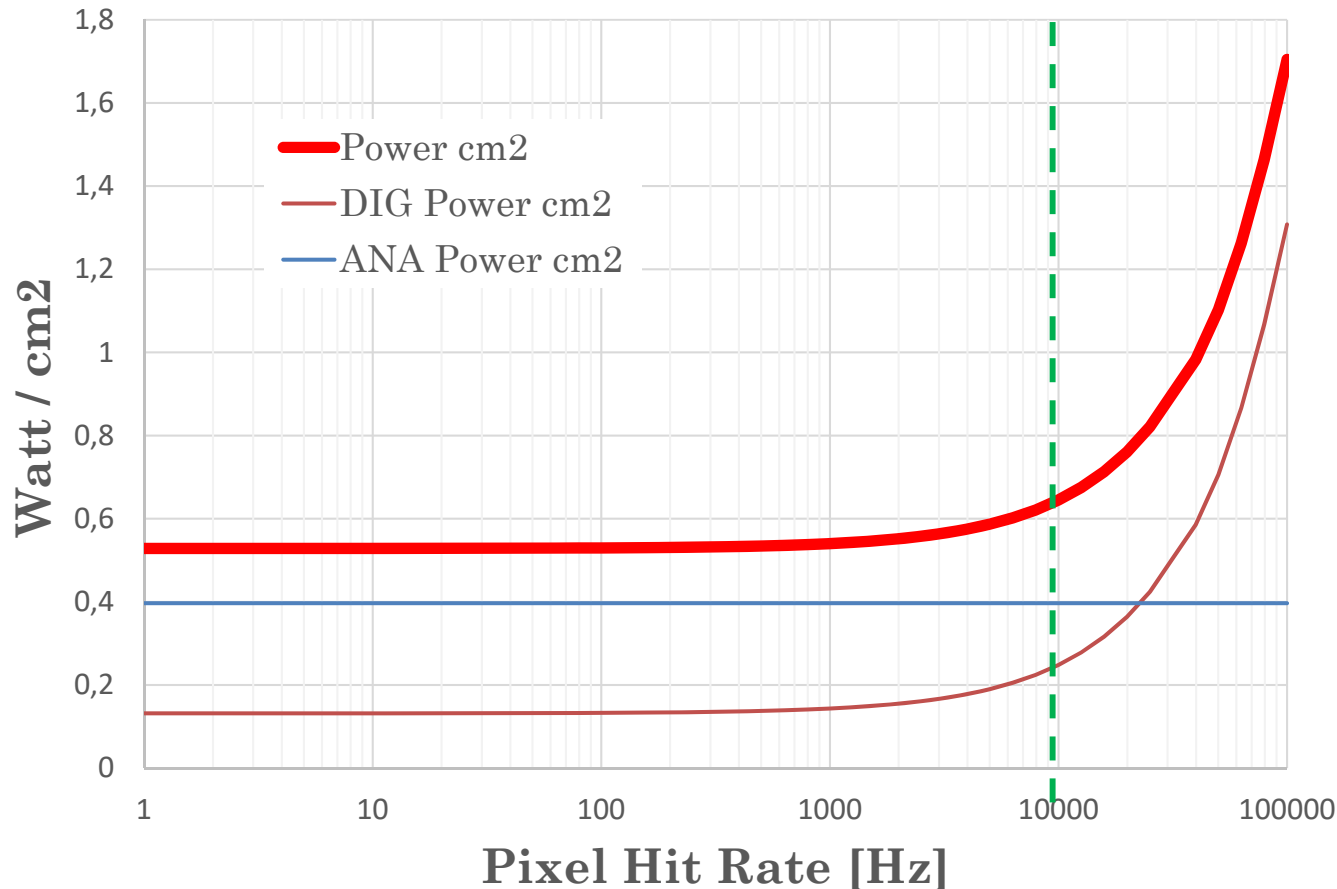
triple-side
Through-Silicon-Via (TSV) I/O pads



➤ the power supply voltage IR drop across the pixel matrix is very low (6.9mV) when a 3-side bonding scheme is used

Timepix4: Dynamic and Static Power Consumption

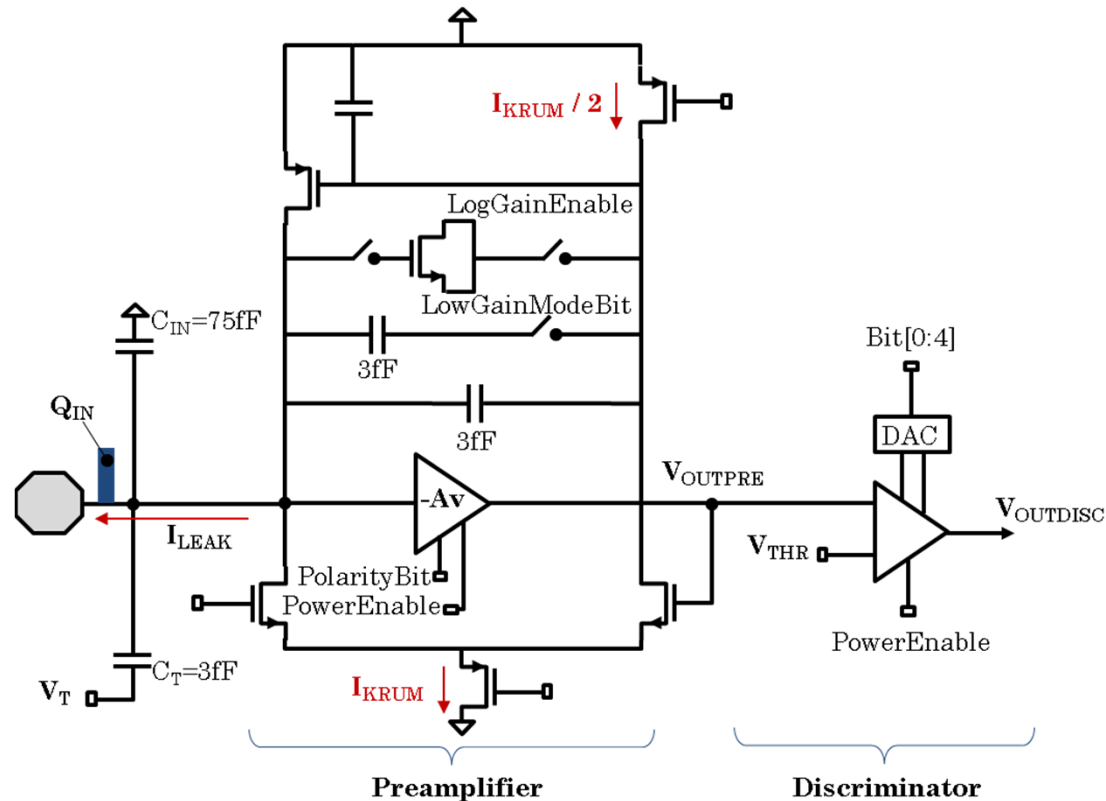
Dynamic and Static Power as a function of hit rate in the Tracking (data driven) readout mode
(simulated by X. Llopart)



➤ the on-pixel analog front-end circuit is the largest contributor to the power budget (9uA/pixel @ 1.2V = 10.8uW/pixel)

Timepix4: Kruppenacher Charge-sensitive Front-end circuit

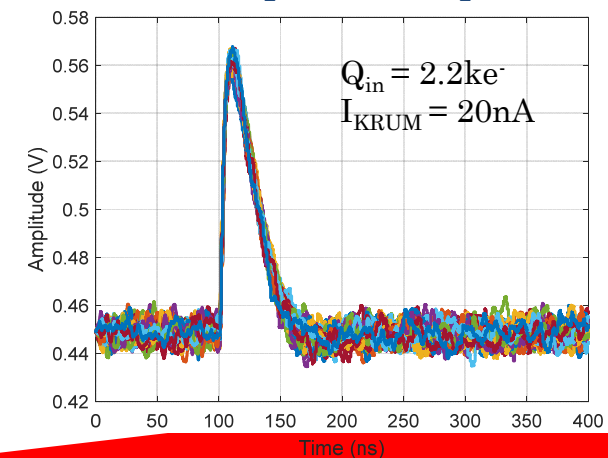
Simplified schematic (designer R. Ballabriga)



Some specifications

Q_{IN} polarity	bipolar
Sensor leakage current compensation	< 10nA
Feedback current (I_{krum})	1nA - 20nA
Hit processing time	$\sim Q_{IN} / I_{krum}$
Gain = $1 / C_{fb}$	adjustable
Input capacitance (C_{IN})	20fF: input pad 45fF: pixel-pad routing (RDL)
ENC @ $C_{in}=75fF$	80e⁻ rms
$\Delta ENC / \Delta I_{LEAK}$	4e ⁻ / nA
Hit arrival time uncertainty	<60ps rms @ $Q_{IN} > 10 ke^-$
Power consumption	preamp: 4uA @1.2V discr: 5uA @1.2V

Preamplifier output

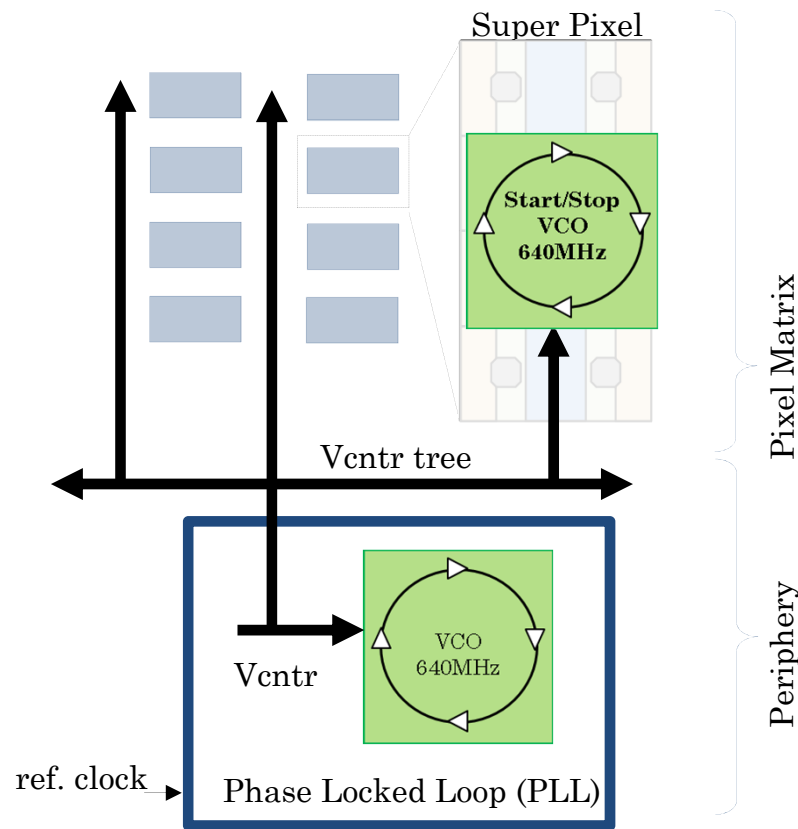


➤ the versatile front-end :

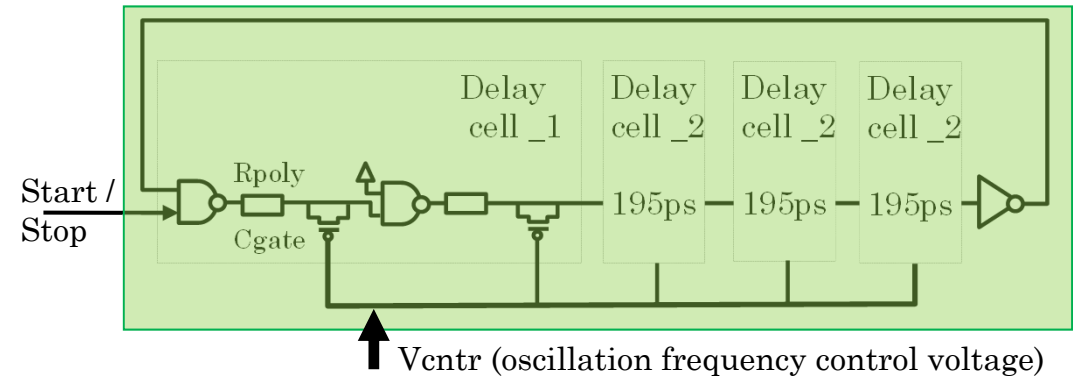
- is compatible with various sensors (solid-state, gas-filled ...)
- optimized for high hit rate operation (dead time < 200ns)
- optimized a 195ps hit arrival time accuracy

Voltage-Controlled Oscillator (VCO)

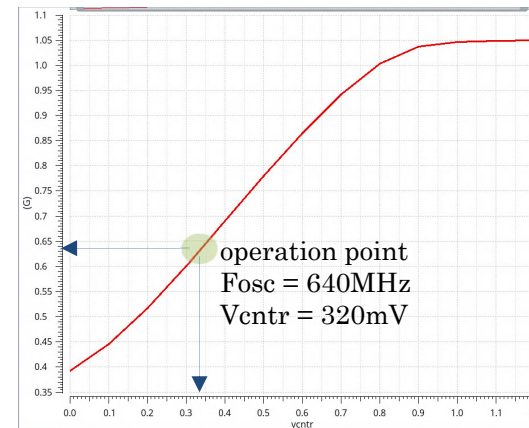
VCO control schema



VCO schematic



VCO control characteristic: $F_{osc}(V_{entr})$

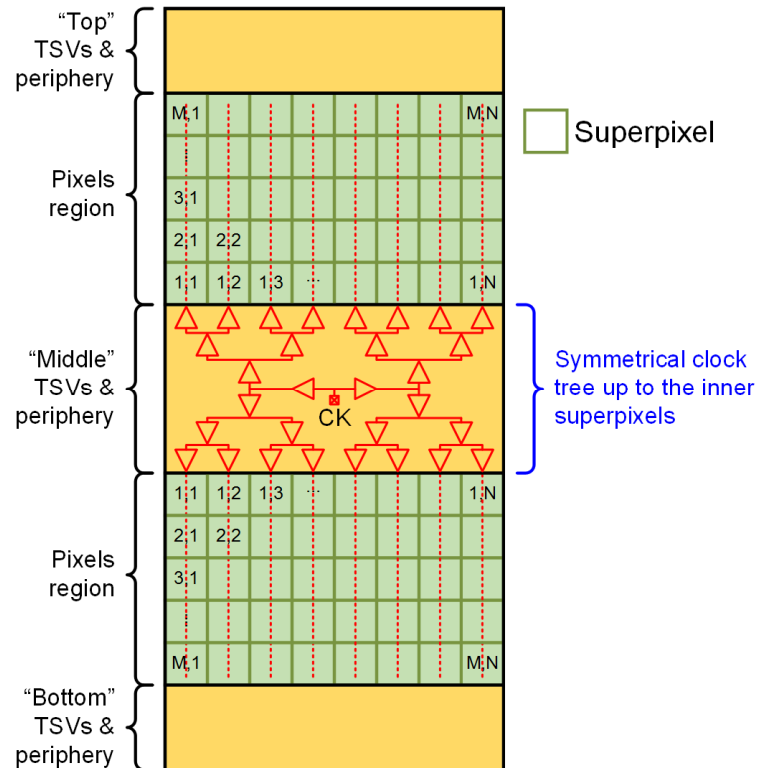


- the VCO consists of 4 RC-delay cells taking only 1% area in the layout of the pixel matrix
- the VCO control voltage is generated in the common PLL, locked to the target oscillation frequency (640MHz)
- in this schema the VCO oscillation frequency is immune to the process corner and the temperature variation
- the VCO can also be tuned individually to compensate for the fabrication mismatch in the range 2.5%
- a $\pm 1\text{mV}$ dynamic voltage drop on the power supply busses will not causes an error more than 1/2 LSB

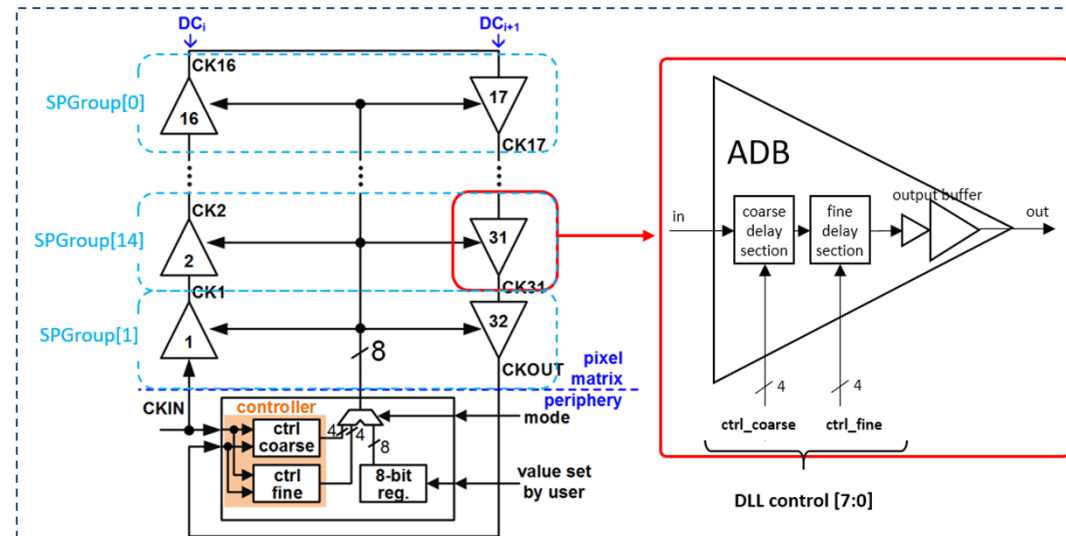
Reference time clock delivery to the on-pixel TDC

<https://iopscience.iop.org/article/10.1088/1748-0221/14/01/C01024/pdf>

Chip-level ref. clock tree



digital DLL per Double Column (designer E. Santin)

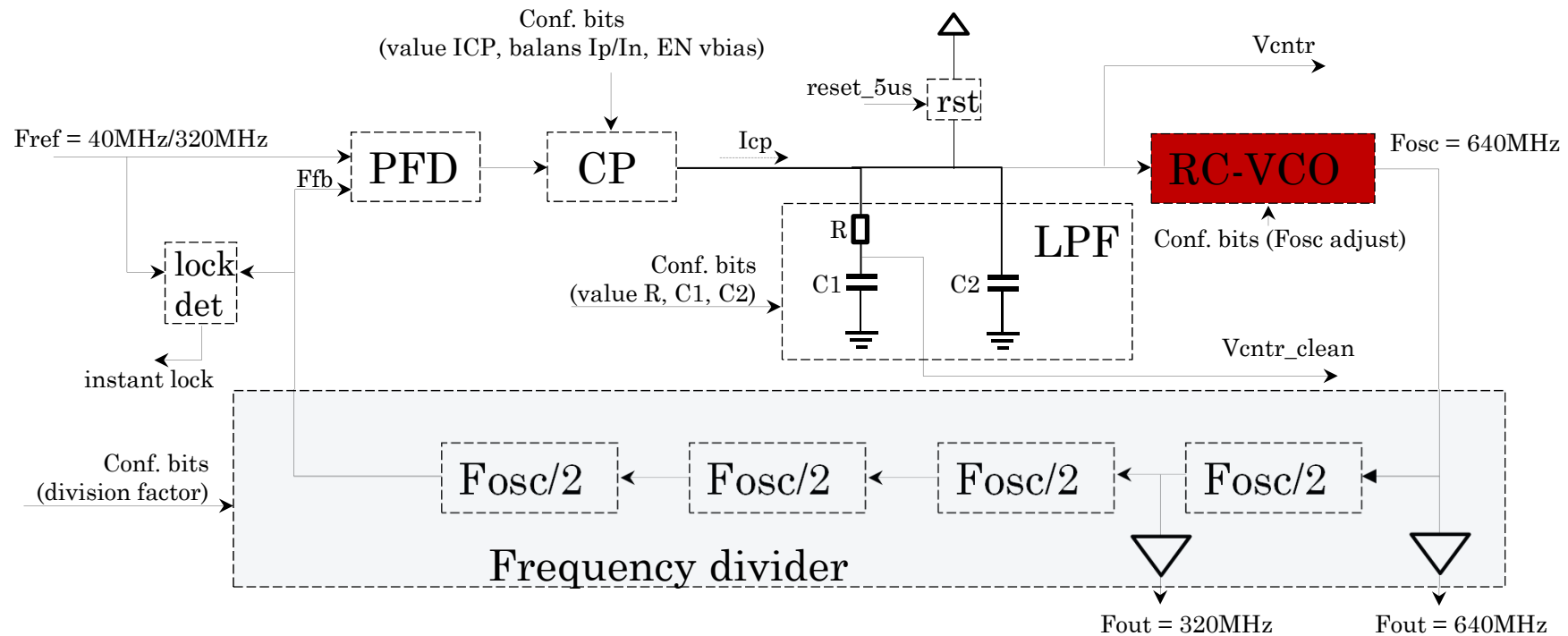


Specifications

reference time clock frequency	40MHz
number of the dDDL blocks per chip	448
SPGroup – to – SPGroup delay	780ps
delay skew uncertainty	< 100ps
total power per chip (dDLL contribution)	157mW

➤ the reference time clock is delivered to each on-pixel TDC with an uncertainty less than 100ps

Timepix4: Generic PLL



➤ used as :

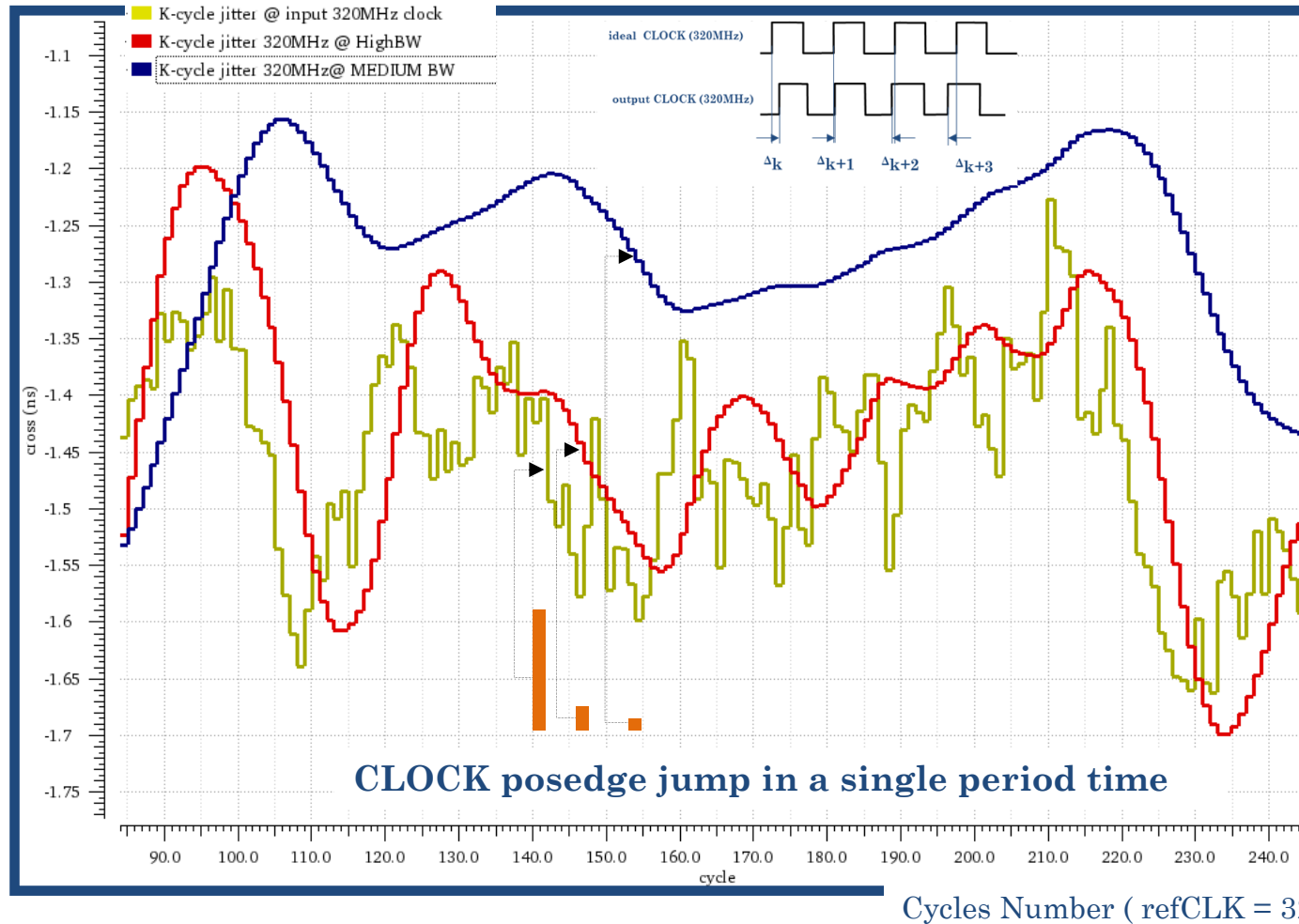
- reference PLL to generate V_{entr} for the on-pixel VCOs
- a 320MHz/640MHz clock generator for the periphery logic
- a 320MHz clock-cleaning PLL in the high-speed (5/12/10.24Gbps) data serializer block

internal time jitter : < 50ps p-p

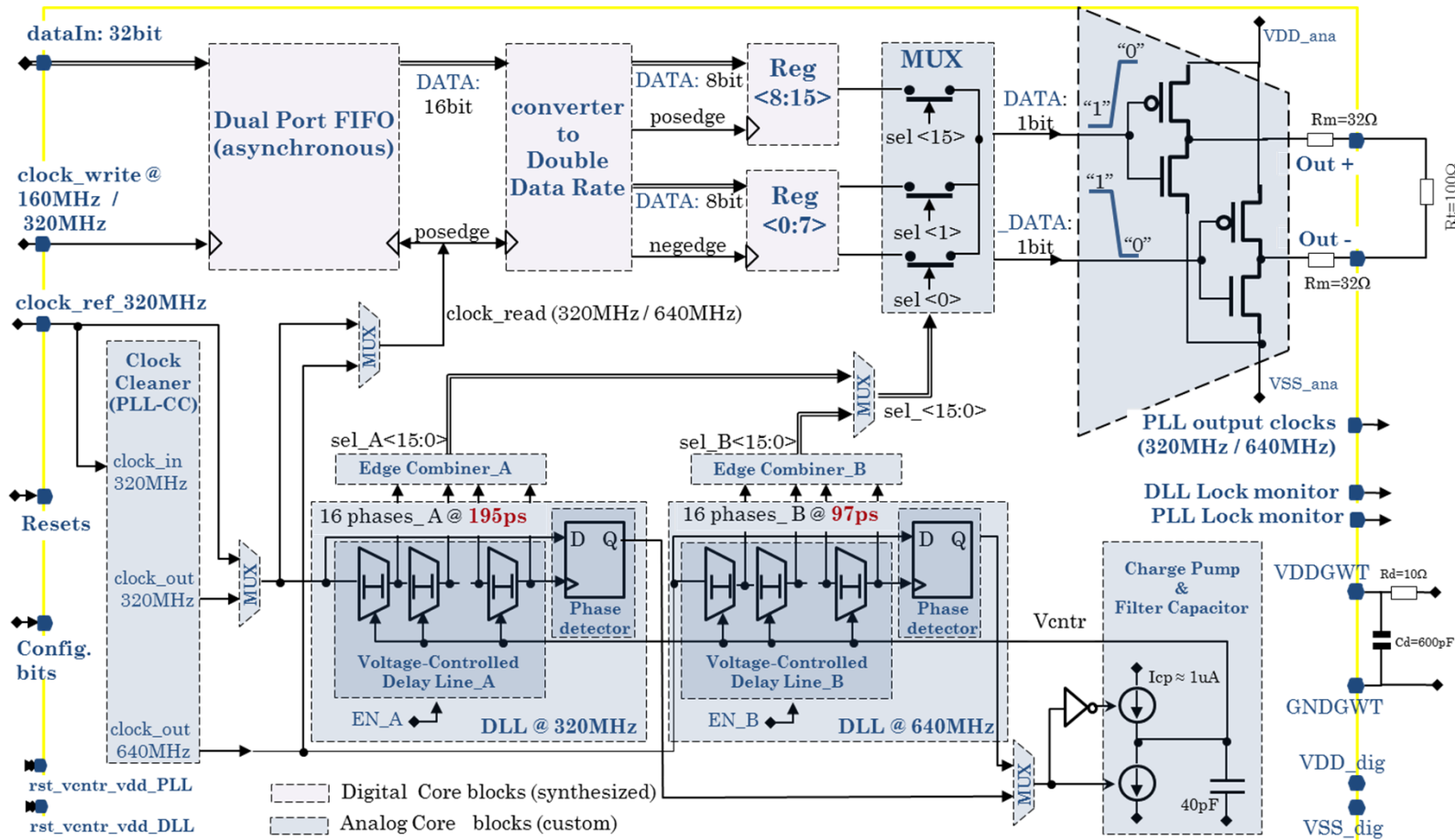
- MOSCAP_rf25 thick gate oxide capacitance (low leakage)
- DNW for better substrate isolation
- separate power supply voltage domain

Clock-cleaning PLL configuration

Suppression of the jitter of the reference clock

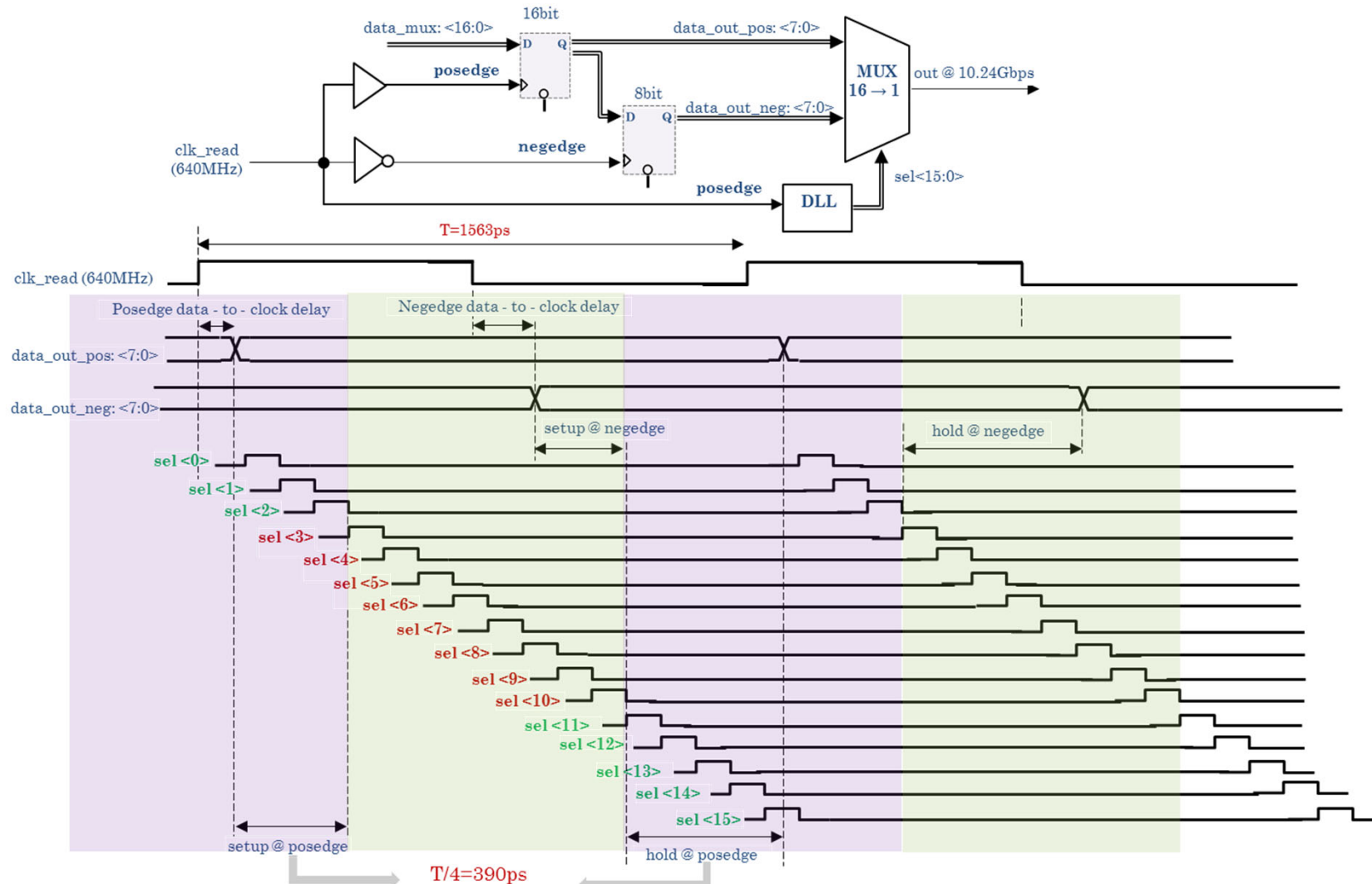


- high-frequency jitter = sudden jumps of the clock edges will be suppressed by the PLL-CC circuit
- low-frequency jitter = long-term (accumulated) shift of the clock edges will be suppressed by the off-chip in the clock-and-data recovery circuit (CDRPLL)



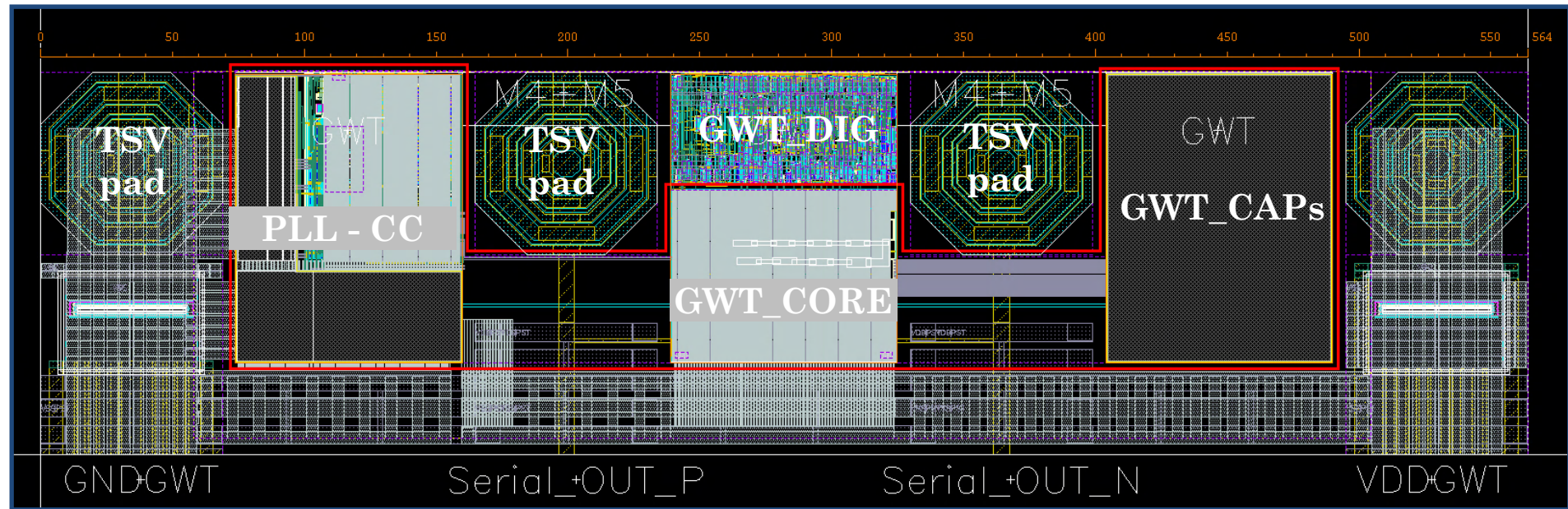
- successor of block used in the VeloPix
- selective data rate: 5.12Gbps/10.24Gbps
- bypassable clock-cleaning PLL (ring-oscillator) : internal jitter < 30ps p-p
- NO high-frequency external clocks: ≤ 320MHz
- voltage-mode transmitter: output swing = ±0.6V @ Rterm=100Ω
- low power : 24mW

GWT-CC: 1/16-Rate Multiplexer-based architecture



- 16-bit input data: byte-interleaved internally (both-edge-clocked)
- internal DLL used to generate 16 phases controlling the Multiplexer

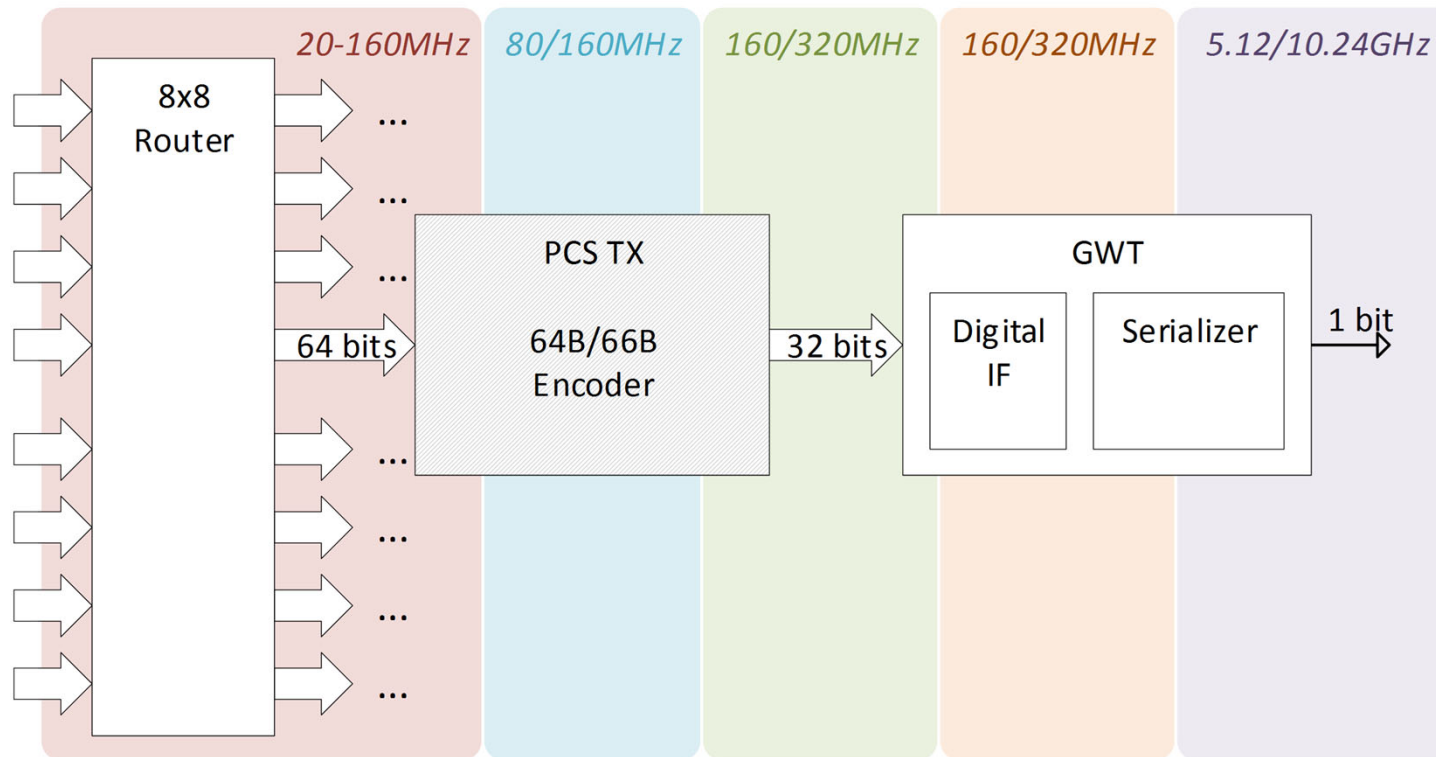
GWT-CC: layout



- **area: $4 \times 10^4 \mu\text{m}^2$**
- **local (dedicated) power supply connections : TSV / Wirebond pads**
- **deep N-well (DNW) substrate isolation of the analog cores**
- **current-leakage-free large-area capacitances: thick gate-oxide varactor**
- **local power supply grid M4/M5**

Timepix4: Physical Coding Sublayer Transmitter (PCS TX)

Top-level diagram (designer A. Vitkovskiy)



Features

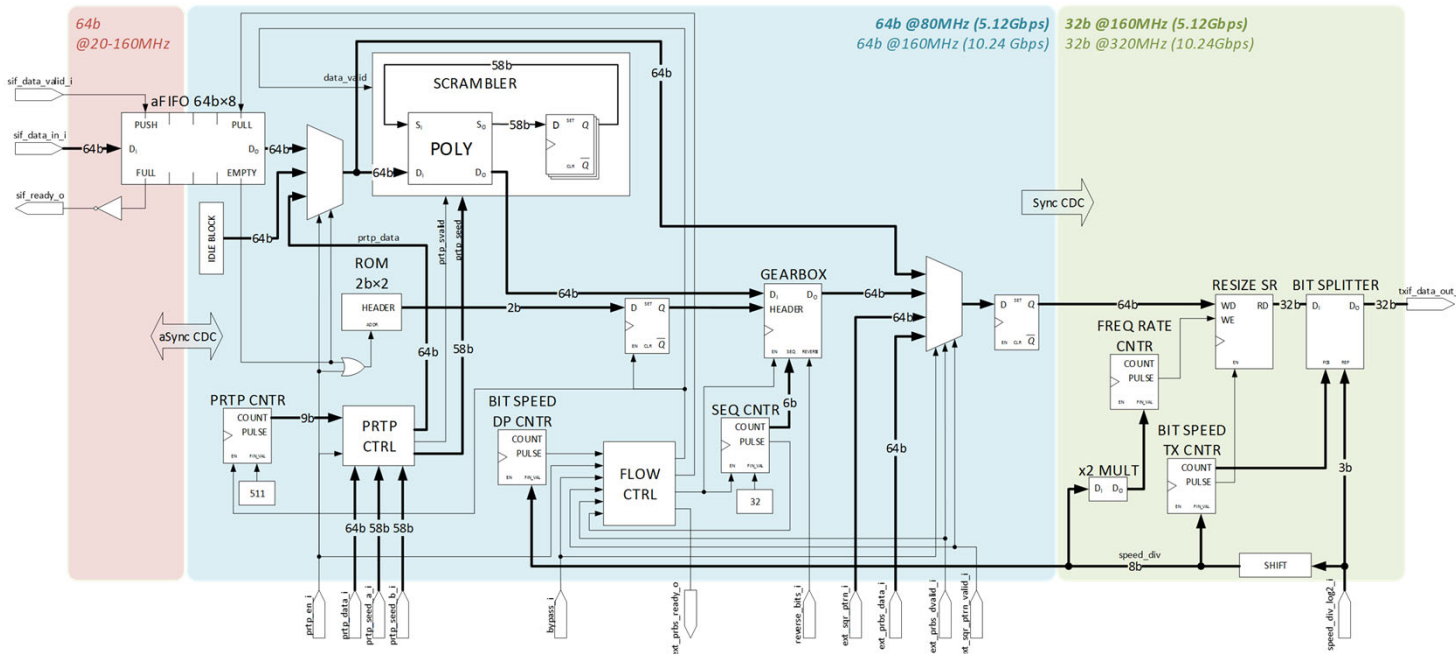
- ☐ 64B/66B data Encoder
 - IEEE802.3ae standard
 - packet starts with LSB / MSB
 - 3.125% data overhead
 - data packet alignment
- ☐ Encoder bypass mode
- ☐ Data scrambling
 - initial value is a zero-vector
- ☐ Serial data speed control
 - by multiplying data stream bits
 - 5.12/10.24Gbps → 40/80Mbps
- ☐ Test pattern generation
 - square wave
 - pseudo-random
 - PRBS-31, PRBS-23, PRBS-15, PRBS-7

➤ provides an interface between the Packet Router block and the GWT-CC block

Timepix4: implementation of the PCS TX block

Block diagram (designer A. Vitkovskiy)

Features



- ❑ Input Asynchronous FIFO :
 - clock-domain-crossing
 - data backpressure compensation

- ❑ Scrambler:
 - randomizes the bit stream for disparity correction between 1's and 0's

- ❑ Pseudo-Random Pattern Controller :
 - enables test mode

- ❑ Gearbox:
 - add 2 bits synch header
 - transmits 32 data blocks in 33 clock cycles to keep a 64b input/output data stream

- ❑ Bit Splitter :
 - serial speed control by repeating of the bits in the data stream

- this highly-configurable and multi-functional topology makes the readout of the chip compatible with various telecommunication standards and computer networking technologies (10 Gigabit Ethernet)
- the bandwidth of the data transfer is fully digitally-controlled

Timepix4: Analog blocks (periphery)

- 12-bit $\Sigma\Delta$ ADC (designer R. Casanova)

Monitoring 12-bits Fully Differential Second Order

Incremental Delta Sigma Converter ADC for Timepix4” – TWEPP 2019

spec: conversion rate up to 1190 samples / sec , power: 8uW

monitors internal signals:

- internal power supply drop (analog and digital core supply)
- BG and temperature monitor
- DAC Biasing voltages

- BandGap reference circuit (designer S. Michelis)

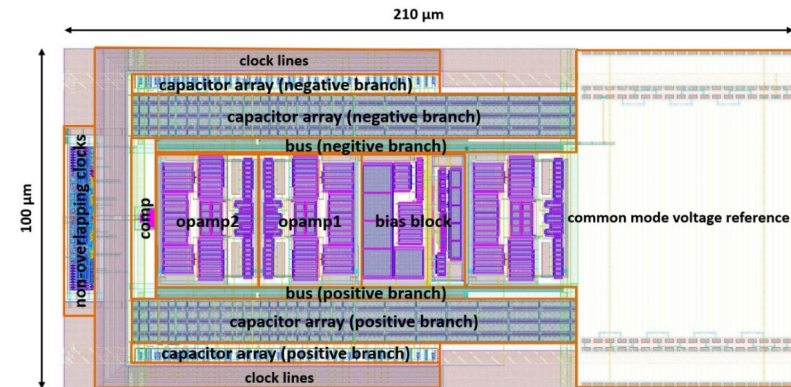
<https://ieeexplore.ieee.org/abstract/document/6872688>

spec: $V_{out} = 330\text{mV}$,

maximum output deviation in absolute value: $\pm 1.1\%$ (process) & $\pm 1.6\%$ (mismatch)

gradient= $6.2\text{uV} / ^\circ\text{C}$, noise = 180uV @ BW= 100MHz ,

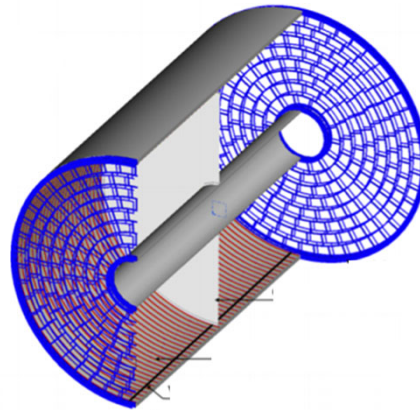
power = 240uW , Enclosed Layout diode



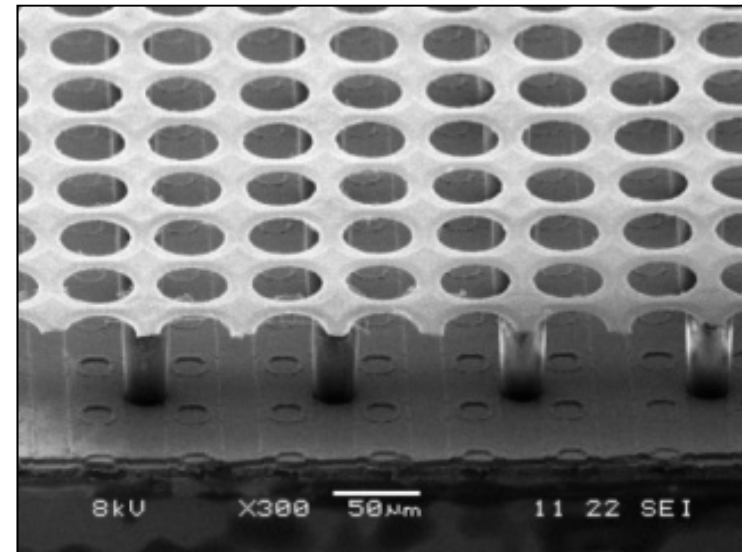
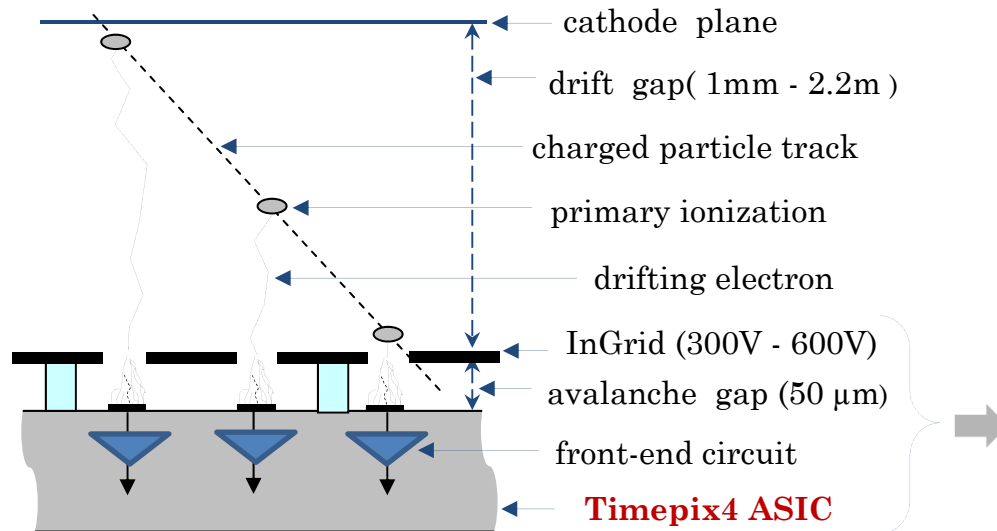
➤ the Timepix4 chip is fully digitally controlled and monitored (NO analog input/output signals)

application
opportunities

2 x 8.7 m² TPC : International Large Detector (ILD)

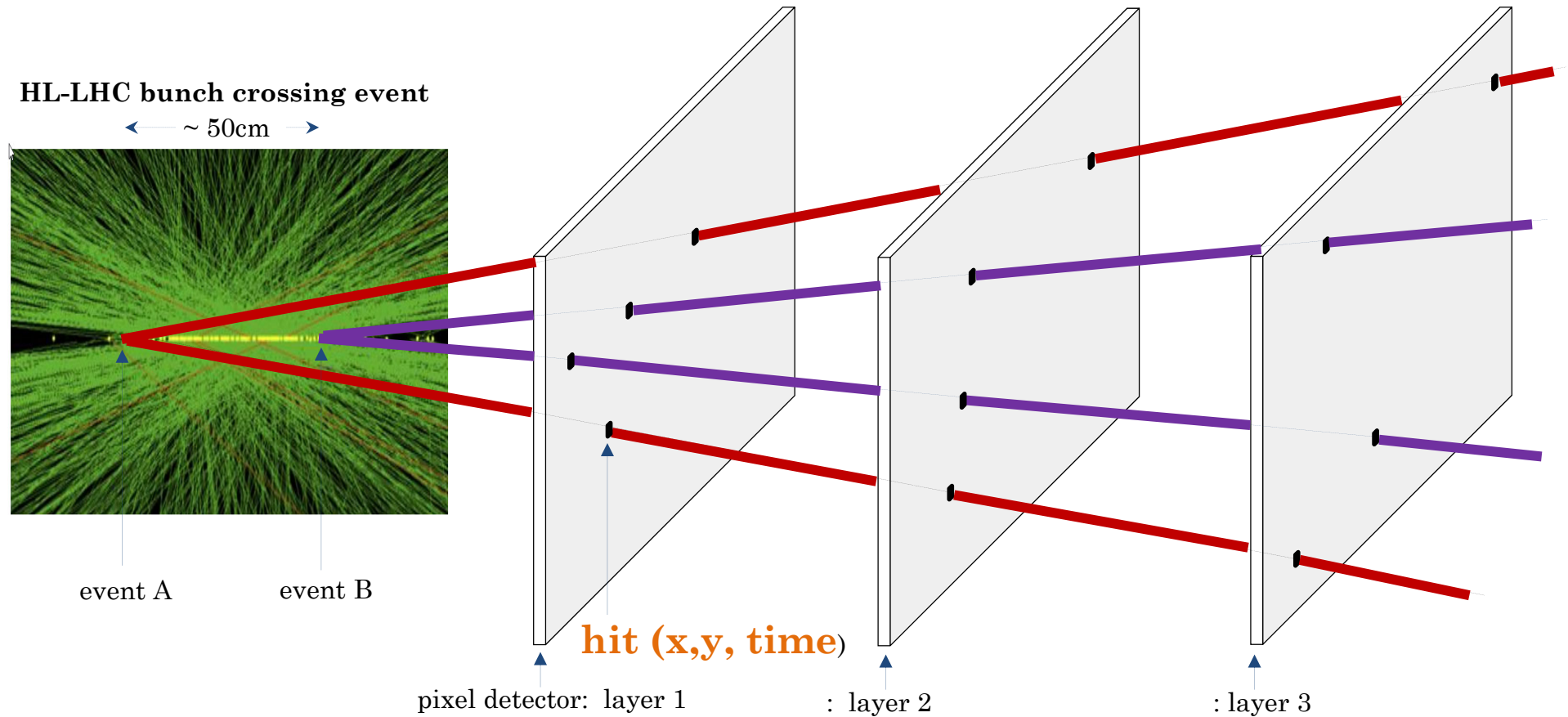


GridPix gas-filled detector : high-resolution 3D track reconstruction



- the Timepix4 ASIC can be used to build large-area TPC detectors
- its small pixel size (55 μ m) & high time resolution (195ps) are useful for 3D tracking

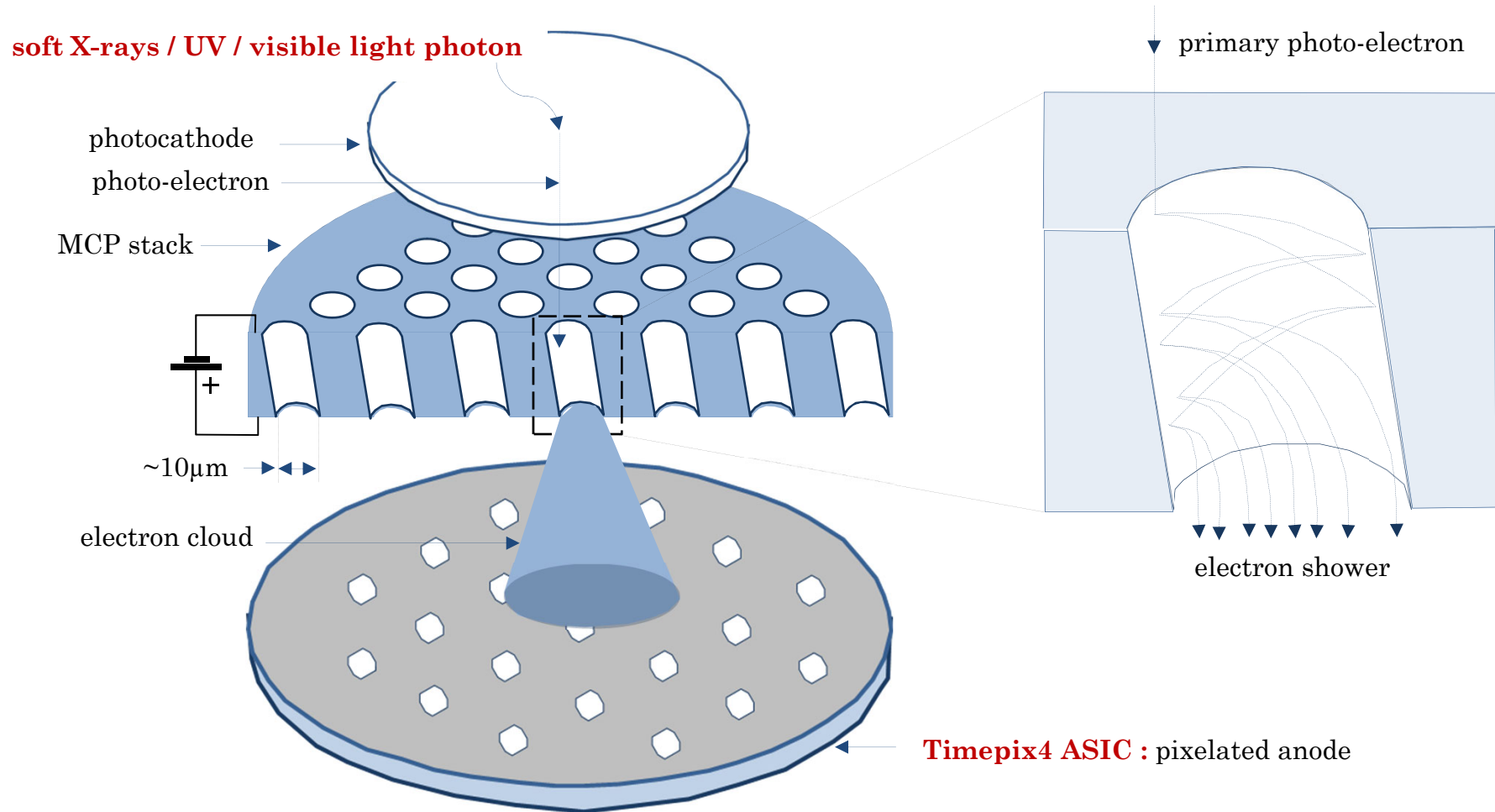
Tracks reconstruction in High-Luminosity environment



- hit time stamp gives an extra dimension in the track reconstruction
- a $< 50\text{ps}$ time resolution is required for efficient 4D tracking in the HL-LHC environment
- the Timepix4 ASIC (195ps time of arrival bin size) will be used as a test vehicle

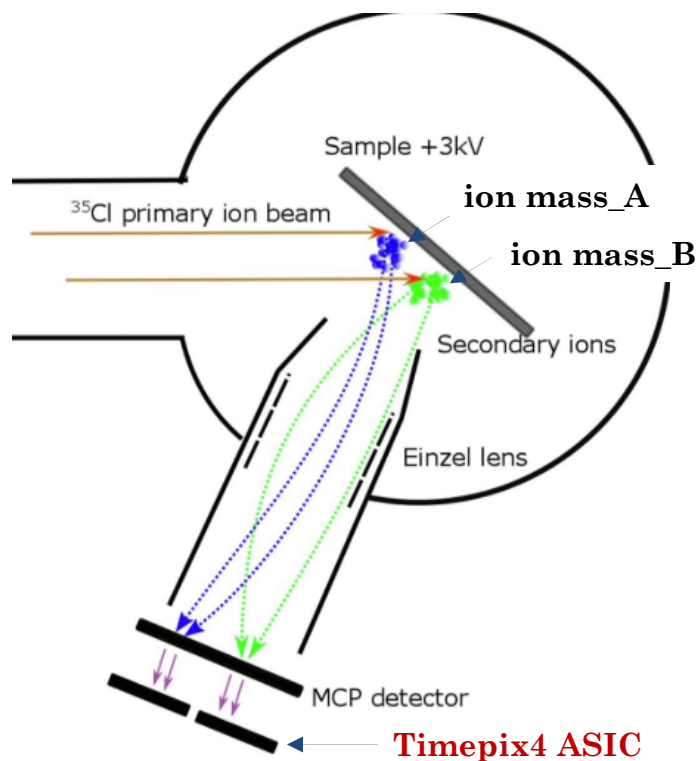
Single-photon imaging detector with sub-100 ps and $< 10\mu\text{m}$ resolutions

<https://doi.org/10.1016/j.radmeas.2019.106228>



- the MCP detector internally has high spatial ($< 20\mu\text{m}$) and temporal ($< 100\text{ps}$) resolutions
- it can fully exploit high position ($55\mu\text{m}$) and time resolution (195ps) of the Timepix4 chip

Time-of-Flight (ToF) mass spectrometer

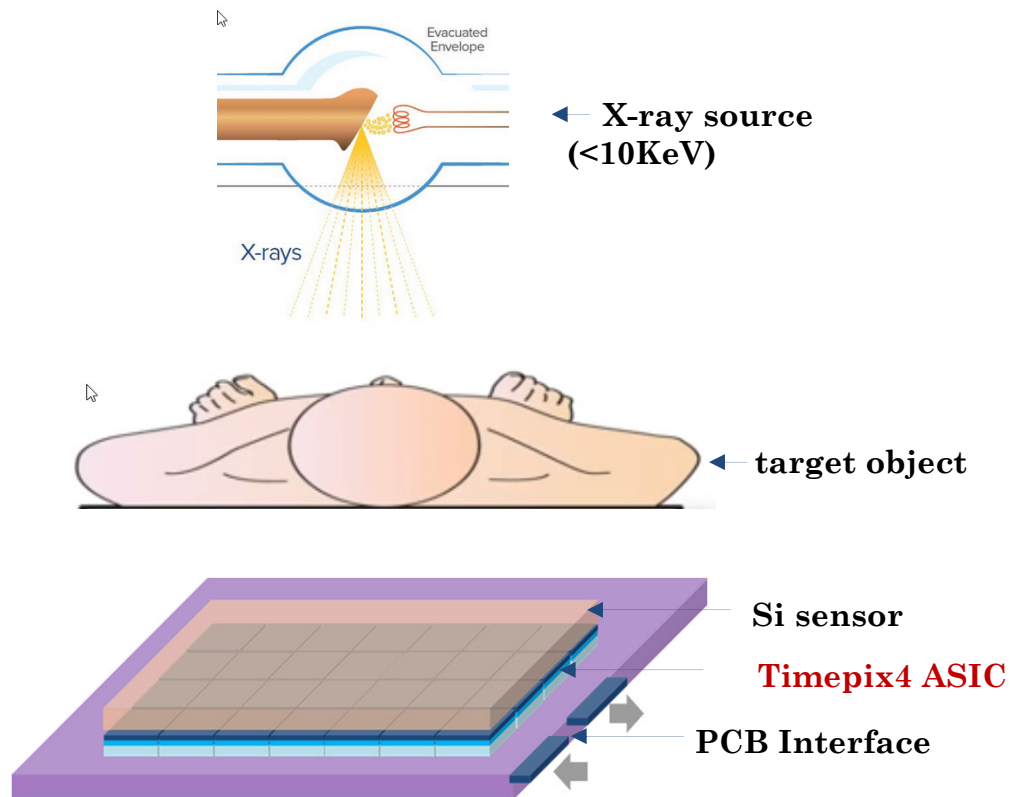


Timepix4 : Tracking (event-based) readout mode

Dead-time free operation	Continuous Data driven readout
Time-of-arrival (ToA) accuracy	195ps
Mass resolution (feasible)	m/dm → 30000
Max Hit rate	3.58 x 10 ⁶ hits/mm ² /s
Spatial resolution (pixel size)	55μm x 55μm

- the time-of-flight (ToF) is used to calculate mass-to-charge value of the secondary ions
- with a 195ps event time-tag in the Timepix4 chip very high mass resolution is feasible

Medical imaging systems



Timepix4 : frame-based readout mode

Dead-time free operation	Continuous Read/Write (CRW)	
On-pixel counter	8 bit	16bit
Max Frame rate	89kFPS	44kFPS
Max Hit rate	$\sim 5 \times 10^9$ hits/mm ² /s	
Spatial resolution (pixel size)	55μm x 55μm	

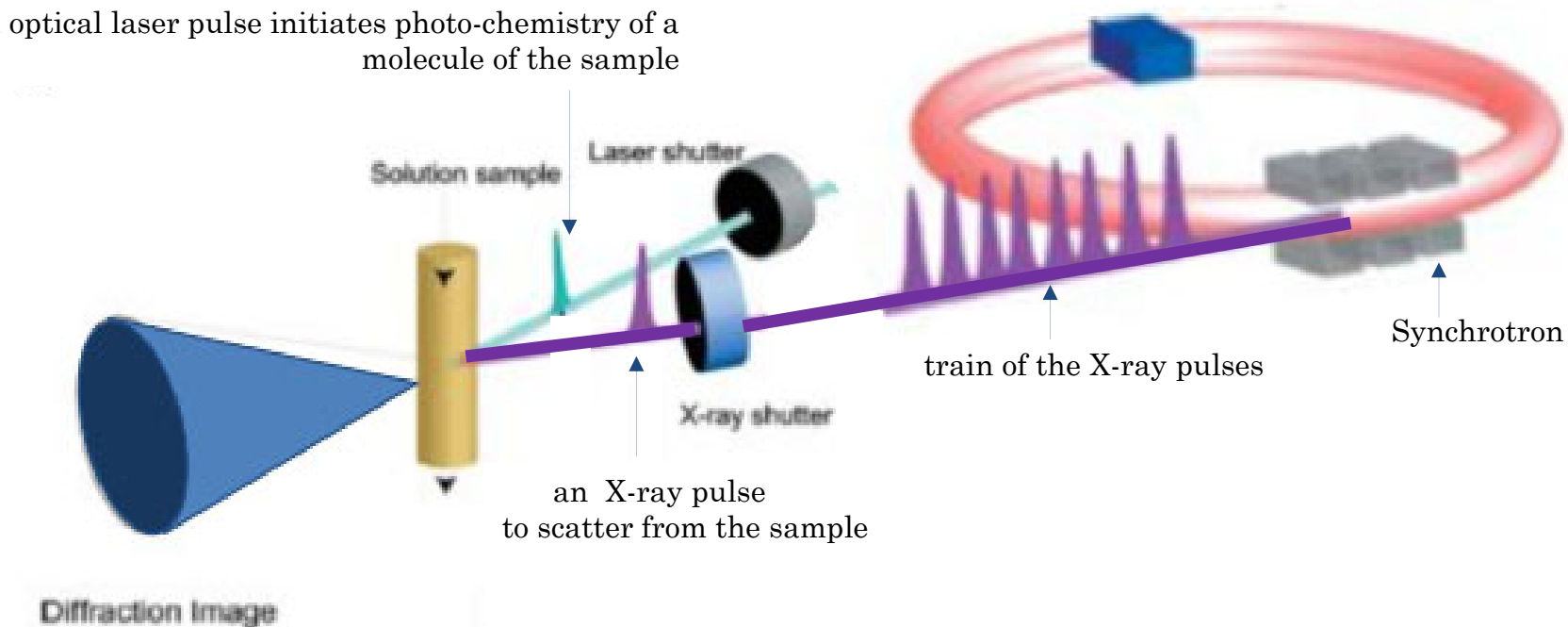
➤ the maximum hit rate is limited by the pulse shaping time in the analog front-end (~200ns) and not by the bandwidth of the readout system

https://www.researchgate.net/publication/320651688_Timepix3_readout_system_for_time_resolved_experiments_at_synchrotron_radiation_facilities

<https://www.intechopen.com/books/advances-in-lasers-and-electro-optics/synchrotron-based-time-resolved-x-ray-solution-scattering-liquidography->

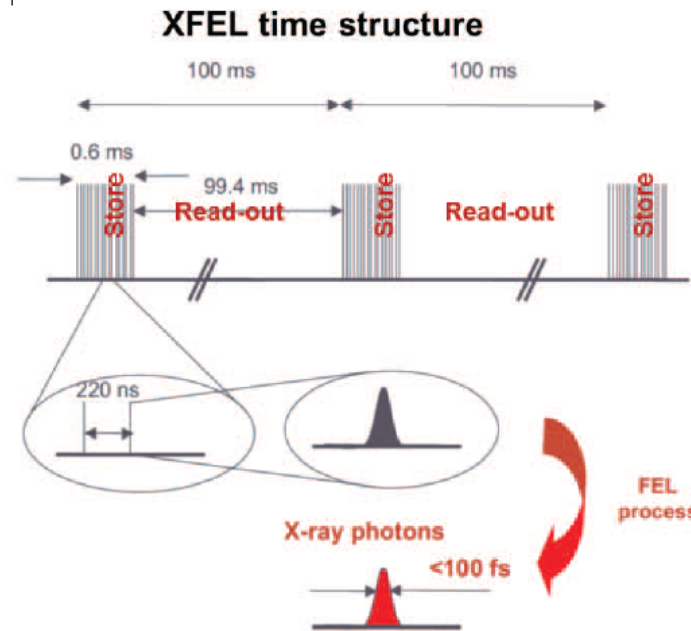
X-ray liquidography: the time evolution of the induced structural changes in molecules

an optical laser pulse initiates photo-chemistry of a molecule of the sample



- the Timepix4 ASIC is very much suitable for a time-resolved diffraction image readout system
- in Tracking readout mode there will be good time resolution between the diffraction images for each X-ray pulse in the train

Timepix4 and the European XFEL facilities

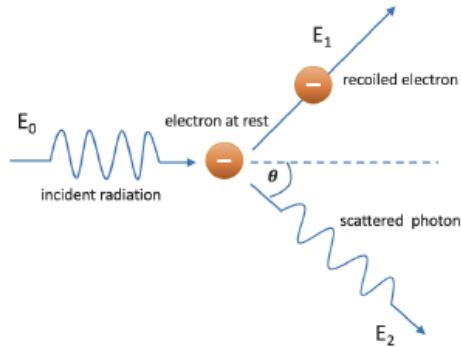


<https://ieeexplore.ieee.org/stamp/stamp.jsp?tp=&arnumber=7581819&tag=1>

	XFEL	Timepix4
Single pulse size / Dynamic range	1 – 1000 photons (12.4keV) per pixel (55um x 55um) 3ke ⁻ ... 3000ke ⁻	500e ⁻ ... 800ke ⁻ (@ log gain mode)
Single pulse processing time	< 200ns	< 200ns (@ Ikrum>10nA)
On-pixel memory depth	2700 X-ray pulses every 200ns in a 600usec train	1-2

- the European XFEL has an extremely irregular time structure of the X-ray flux
- the Timepix4 ASIC is NOT optimized for such operation conditions

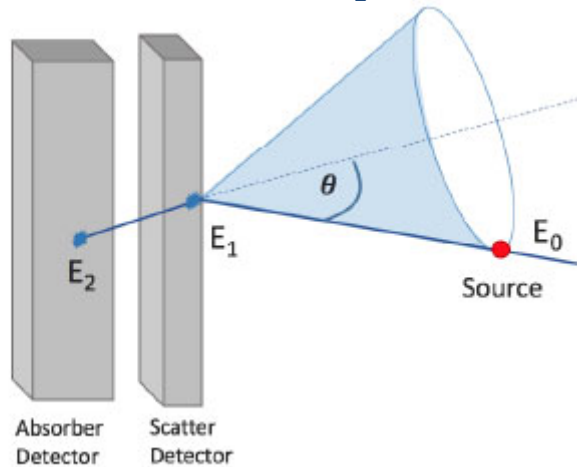
Compton scattering effect



$$\cos \theta = 1 - m_e c^2 \frac{E_1}{E_0 (E_0 - E_1)}$$

$$E_0 = E_1 + E_2$$

Schema of the Compton camera



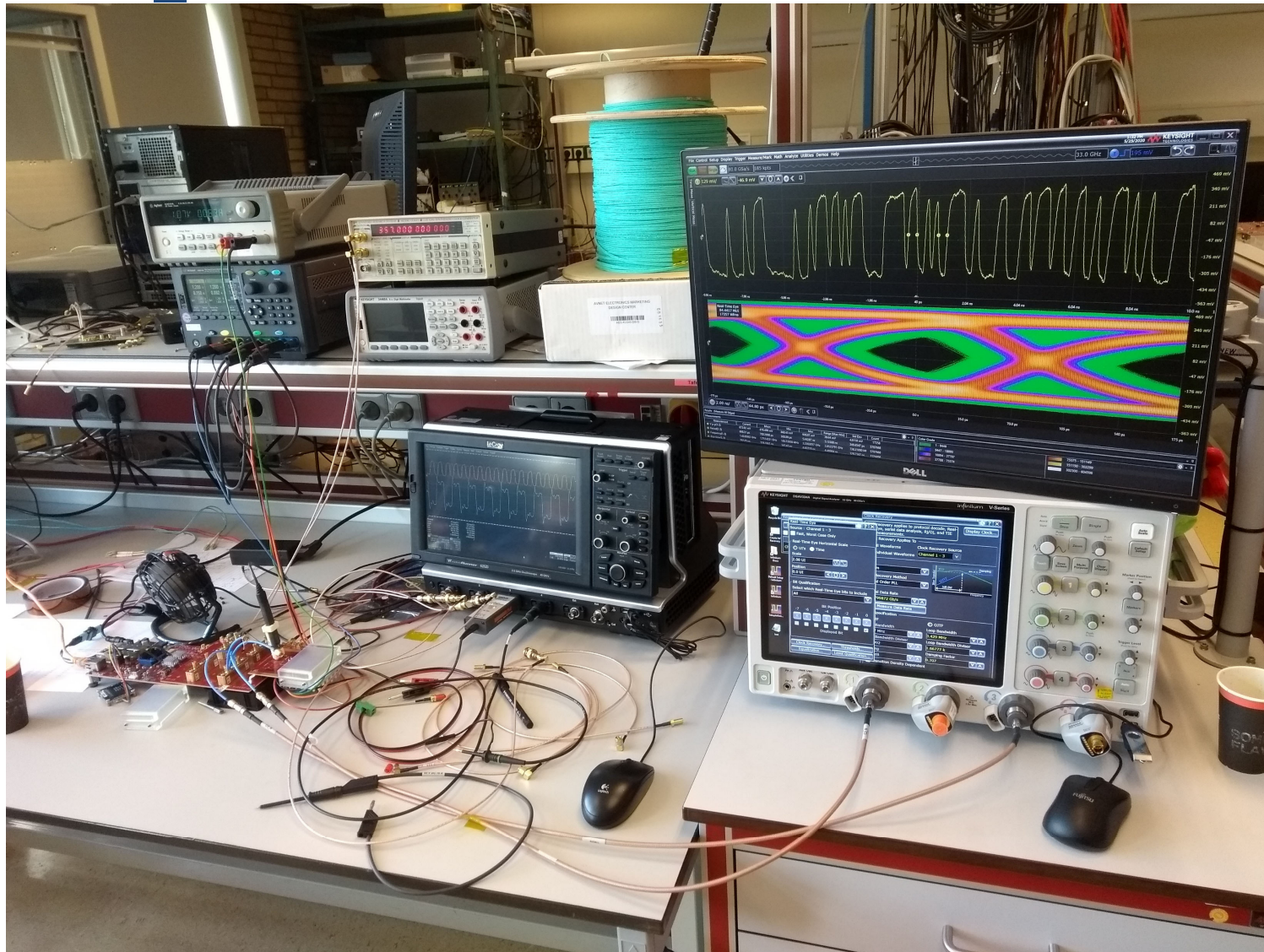
Timepix4:

2D coordinate, energy and time for each single hit

Dead-time free operation	Continuous Data driven readout
Time-of-arrival (ToA) accuracy	195ps
Energy measurement accuracy	300eV rms
Spatial resolution (pixel size)	55μm x 55μm
Max Hit rate	3.58 x 10 ⁶ hits/mm ² /s

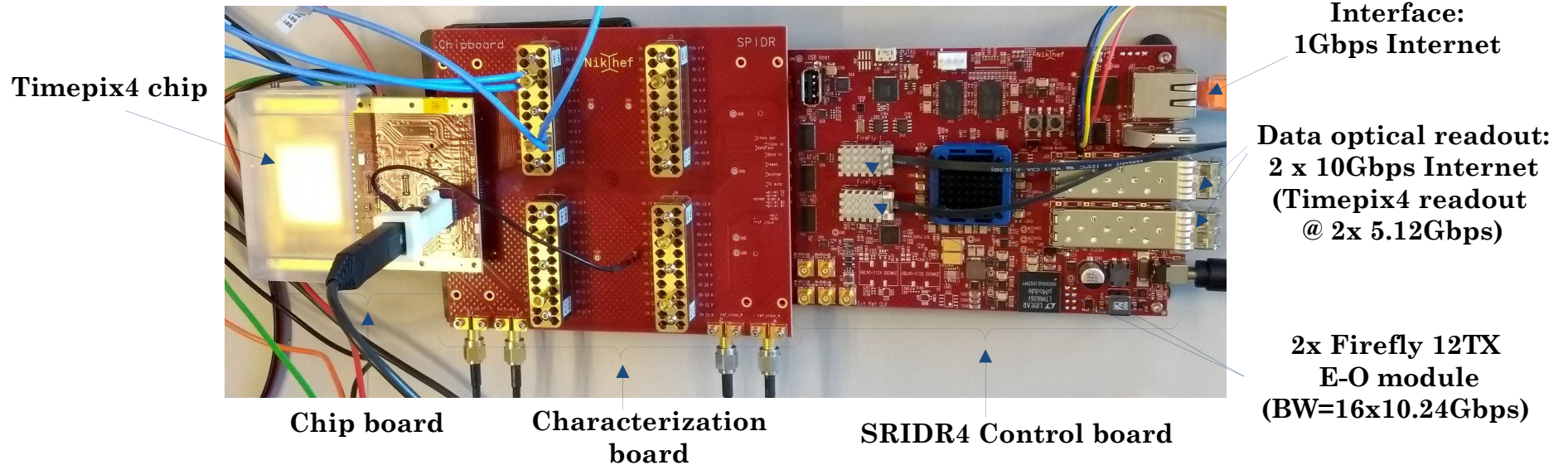
- the Timepix4 ASIC can be combined with different sensors (1mm Si or 2mm CdTe) to build both the Scatter detector and the Absorber detector
- the Timepix4 ASIC delivers a full set of data for each single event needed to estimate the possible direction of the original gamma

experimental results



Timepix4: test system

SPIDR4 control and readout system (designer Bas van der Heijden, basvdh@nikhef.nl)

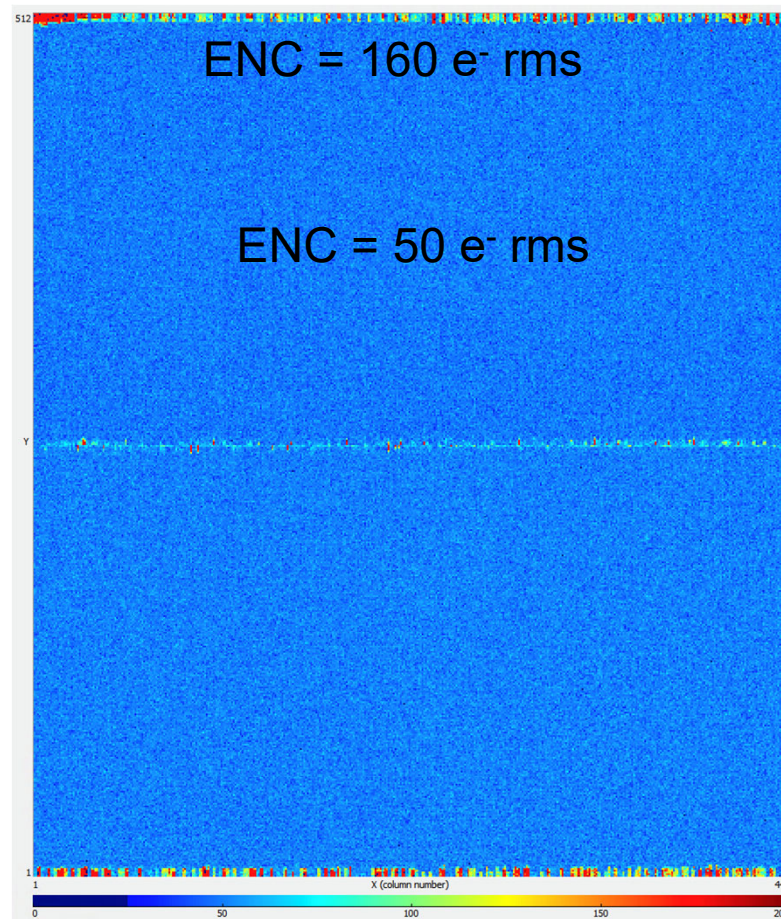


- SPIDR4 readout system from Nikhef
- SPIDR4 Chipboard + Timepix4
- Timepix4 is wirebonded from TOP and BOT periphery WB pads
- Timepix4 accessed (slow control) through TOP periphery
 - Bottom periphery IO is not fully connected due to PCB design error

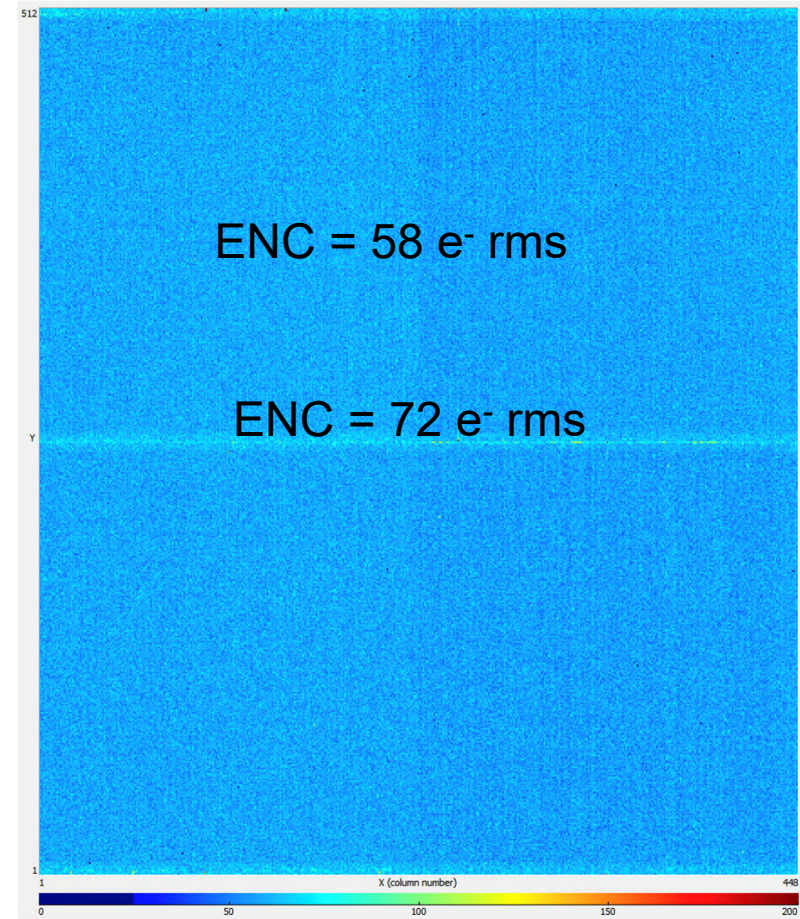
ENC full matrix (X.Llopart)

Timepix4v0

- Excess ENC noise on top of peripheries (x2-4):
 - ~26 rows: [0:7] [250:260] [504:511]

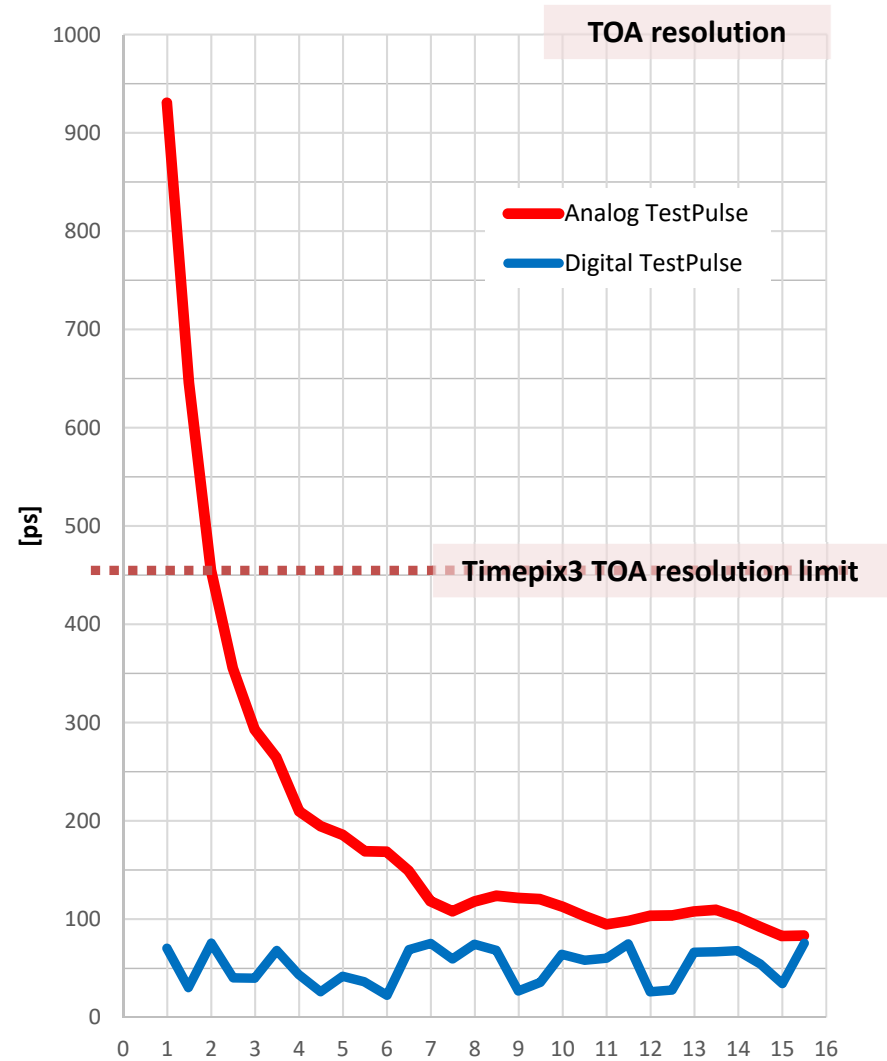
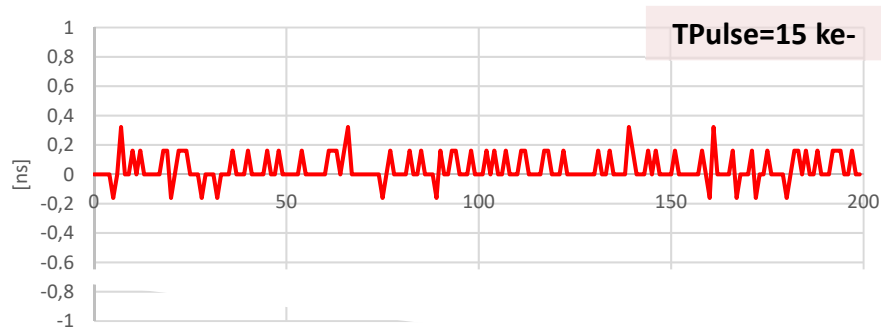
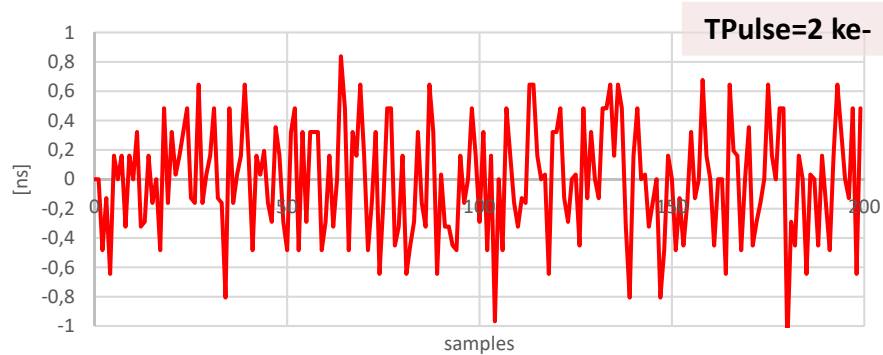
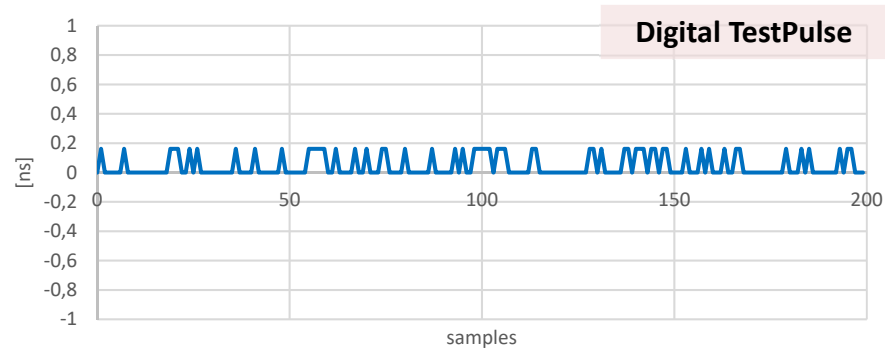


Timepix4v1

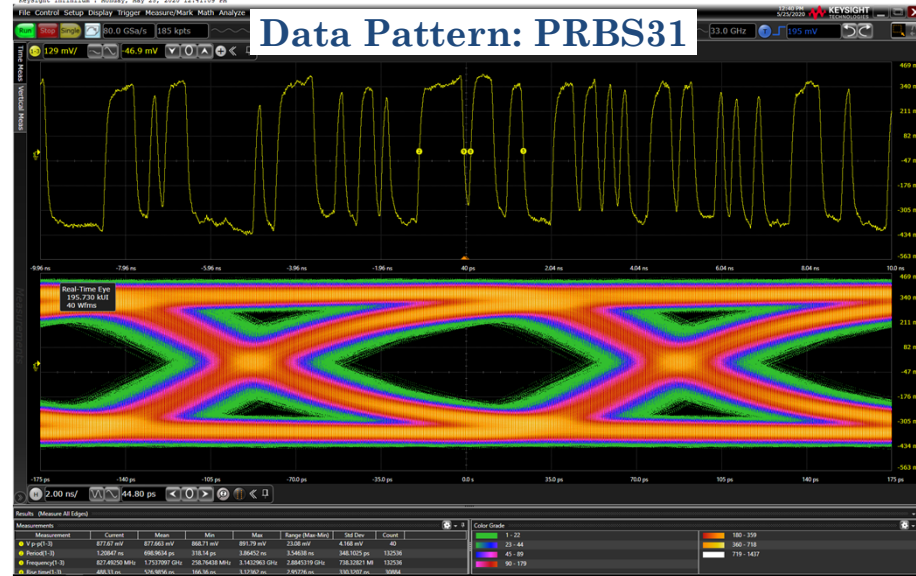
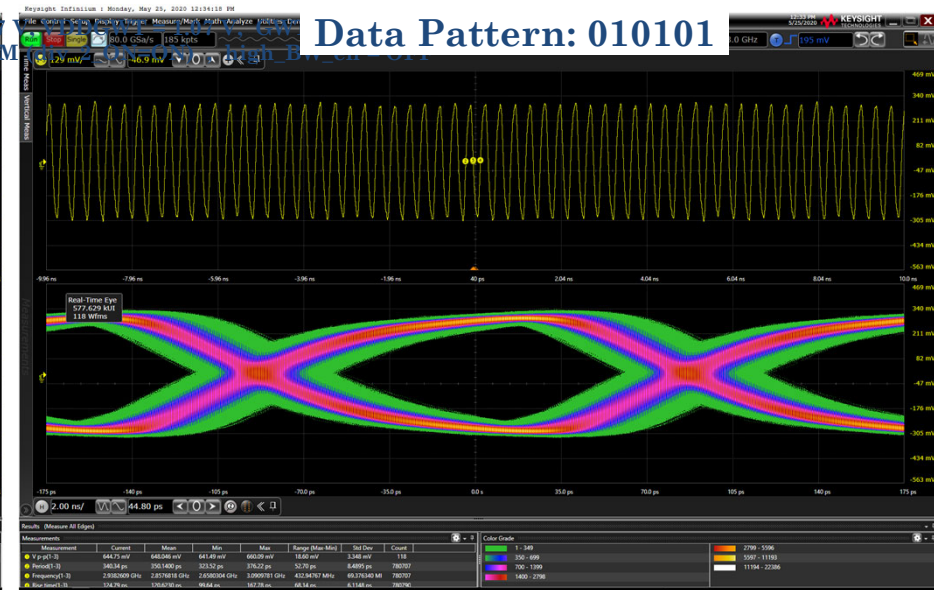
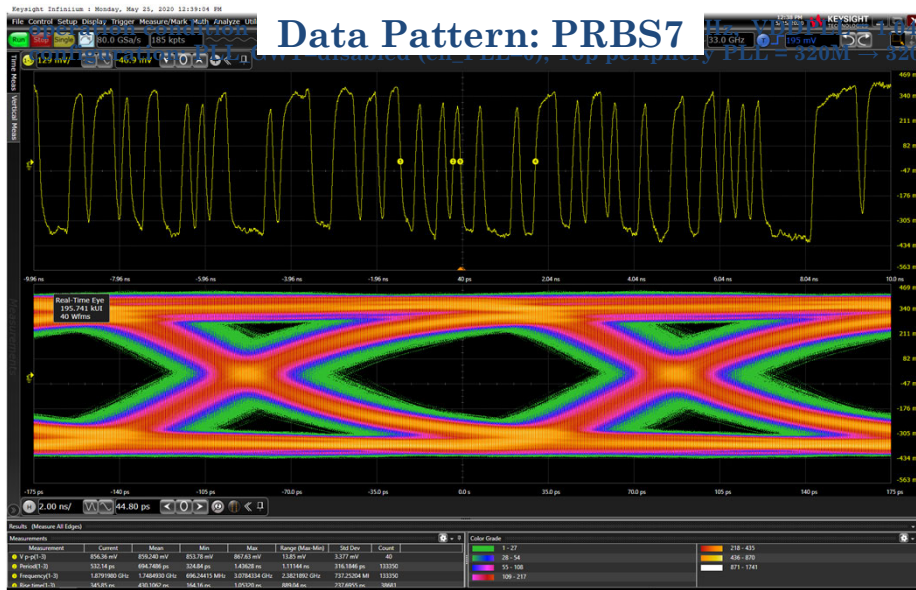


TOA Resolution (X. Llopart)

[TOA-TOT, 1 pixel, 10000 samples, HG e-]



GWT-CC : 5.12Gbps Data Serializer and Wireline Transmitter



➤ the GWT demonstrates good eye diagrams for various data patterns

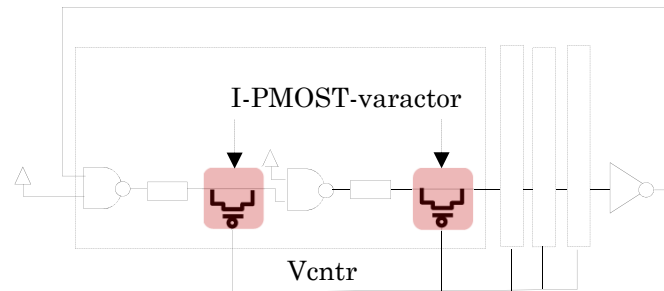
GWT-CC: Bathtub curves and jitter histogram



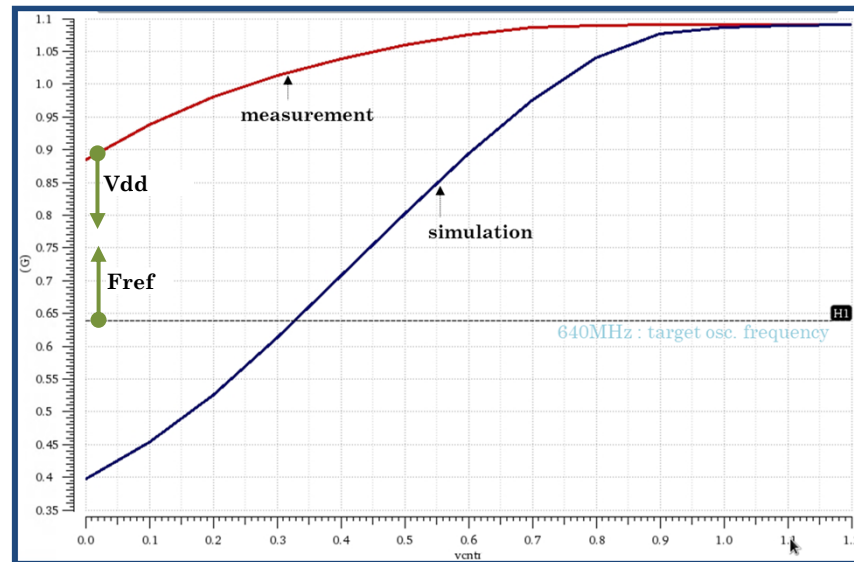
- the scope locks on the PRBS7 orbit
- the shape of the jitter spectrum looks fine
- the sampling clock tolerance @ BER=10⁻¹² is $\pm 0.2\text{UI} = \pm 35\text{ps}$

PLL locking issue

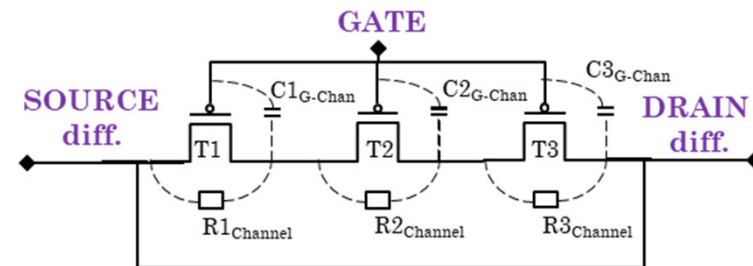
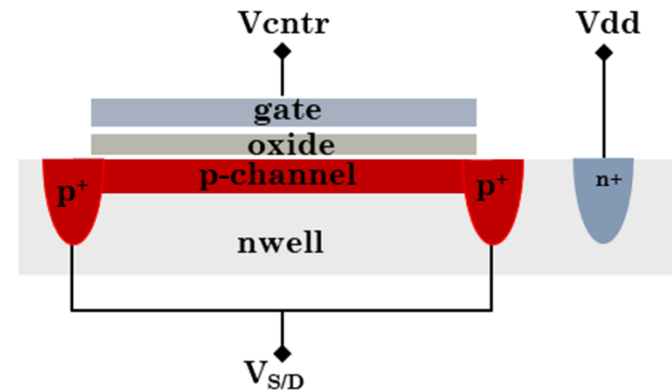
Voltage-Controlled Oscillator



VCO control characteristic : $F_{osc}(V_{cntr})$

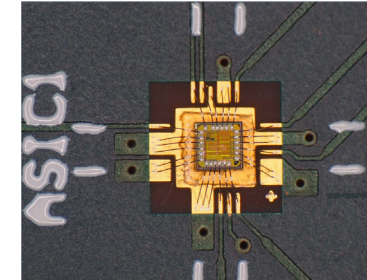


I-PMOST-varactor

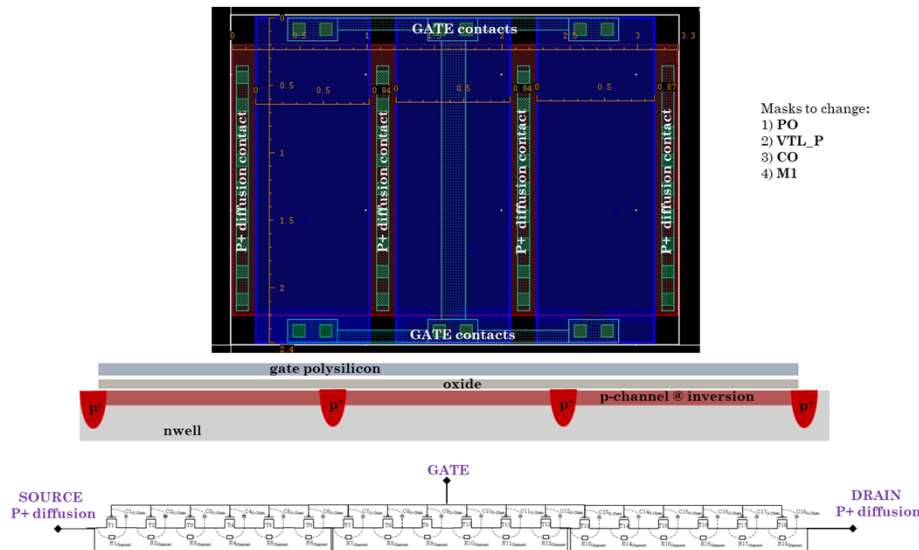


- the VCO control characteristic is critically dependent on the modeling of the varactor capacitance
- a single-device model does NOT take into account the internal channel resistance in the inversion

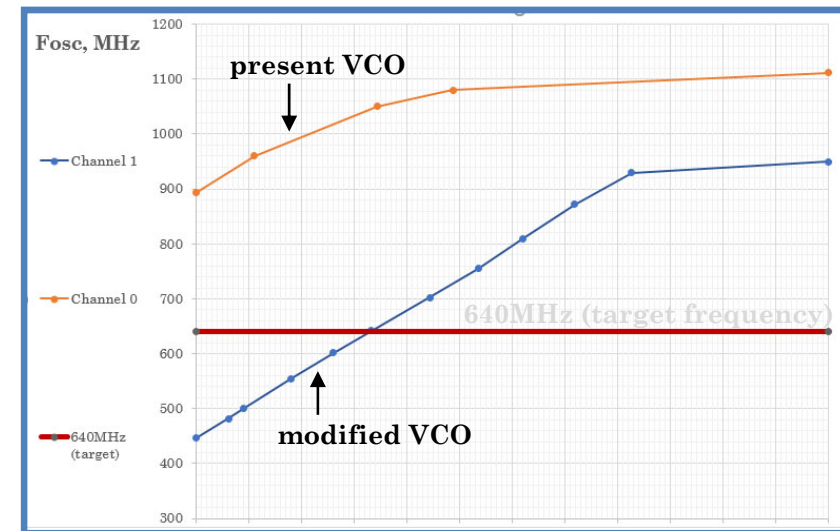
VCO modification : test chip results



New varactor:
(short-channel I-PMOST_LVT-based)



Measurements: Fosc (Vcntr)



- by changing the type of the varactor device and re-arranging the layout to use only short-channel devices it is possible to mitigate the effect of internal channel resistance
- with the new varactor the VCO will reliably lock on the target frequency

Take-home messages

- **Timepix4** is a new readout chip for the hybrid pixel detectors to be used in both the **photon science and particle physics fields**
- the chip is developed in the frame of the **Medipix4 collaboration**, has configurable architecture to accommodate a large number of different applications
- the chip has the following specification:
 - a **large sensitive area** (6.93 cm^2) with almost no dead area ($<0.5\%$)
 - a **4-side buttable** and therefore suitable for large-area detectors assemblies
 - **in Tracking (data driven) readout mode** :
 - ❖ time measurement ToA: 23-bit dynamic range (1.6ms) @ **195 ps LSB**
 - ❖ charge measurement ToT : 15-bit dynamic range @ **80e⁻ LSB**
 - ❖ maximum hit rate : **$3.58 \times 10^6 \text{ hits/mm}^2/\text{s}$**
 - **in Imaging (frame-based) readout mode** :
 - ❖ Photon Counting per pixel: **8-bit or 16-bit Continuous Read-Write (CRW)**
 - ❖ maximum hit rate : **$5 \times 10^9 \text{ hits/mm}^2/\text{s}$**